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Full 3D Simulations on The New BNL ICDA(3D-Trench-Electrode) Detectors

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OUTLINE

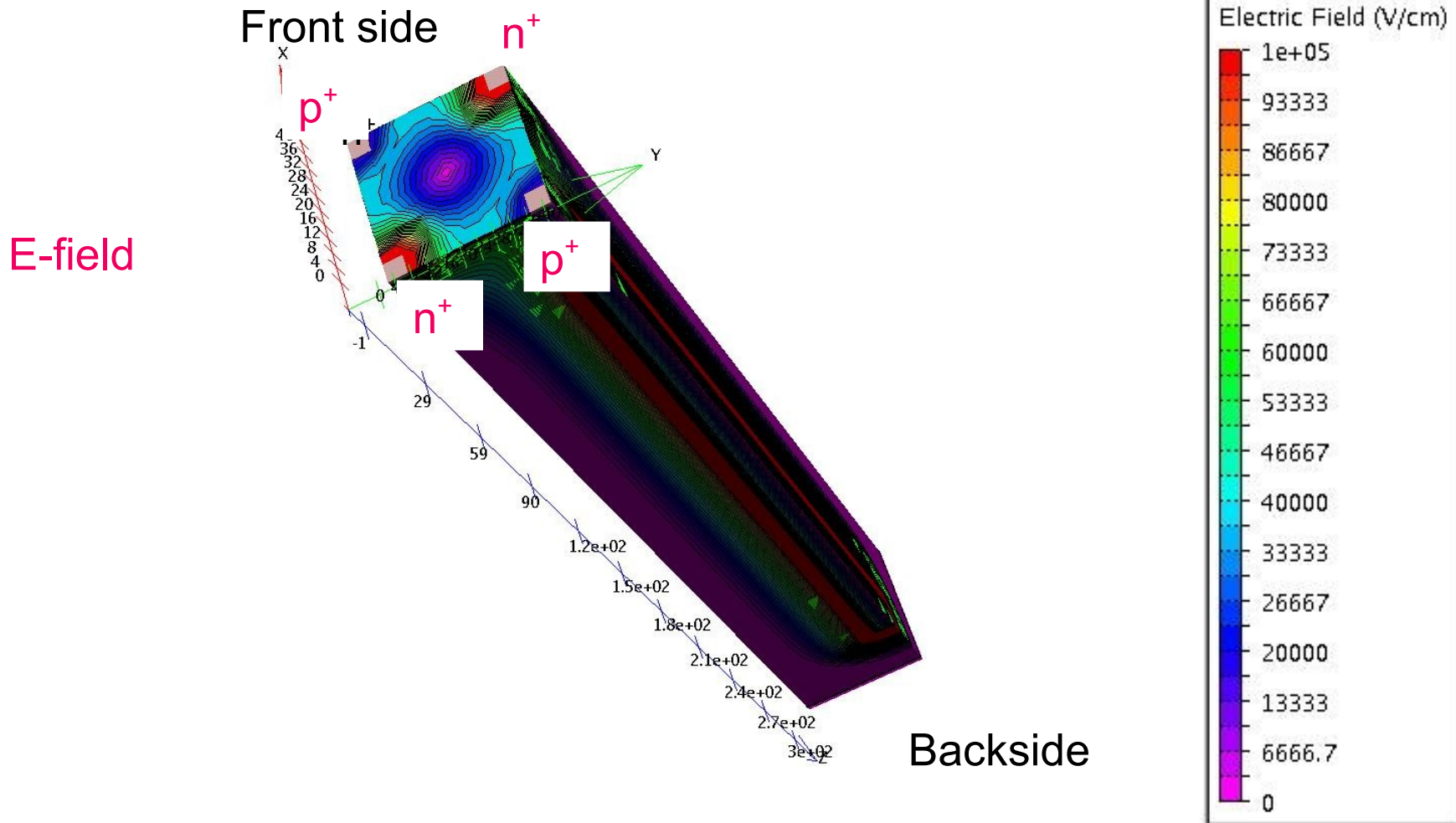
- The New BNL Independent Coaxial Detector Array (ICDA)
- 3D Simulation results
- Preliminary design of the mask set
- Summary

- Complicated and high electric field profiles in conventional 3D detectors with column electrodes

3D simulation of BNL-2C-3D, $1 \times 10^{16} \text{ n}_{\text{eq}}/\text{cm}^2$, 150 V

ATLAS

Data from two_columns_3d_1E16_Lc5um_Lp30um-150V.str



The main advantages of the new ICDA configuration

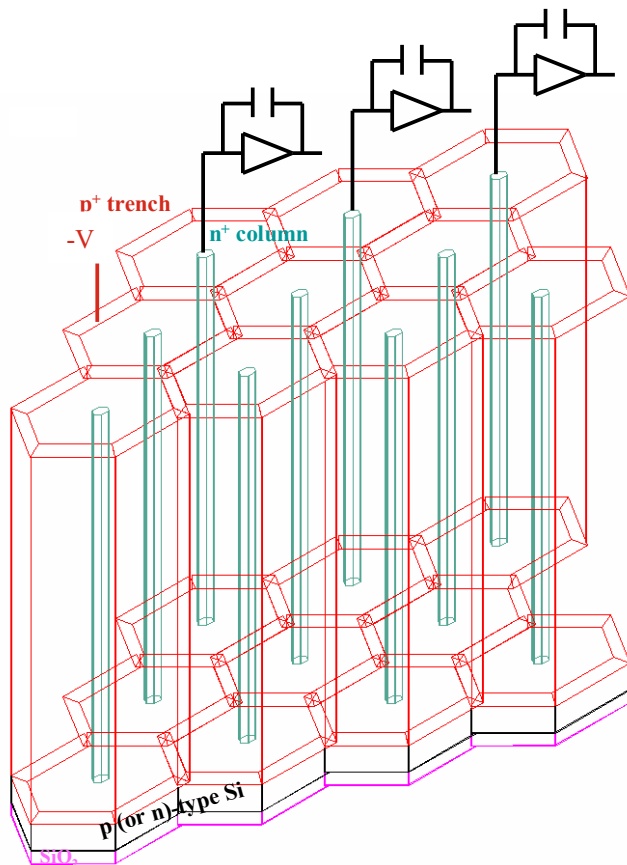
- More uniform, homogeneous electric field
- No saddle points, no low/no field region
- No extremely high field regions near breakdown condition
- Still decoupling thickness from depletion depth (rad-hard and possible to deplete very thick detectors)

•Independent Coaxial Detector Array

(ICDA) ----- US patent pending (1004305-027US)

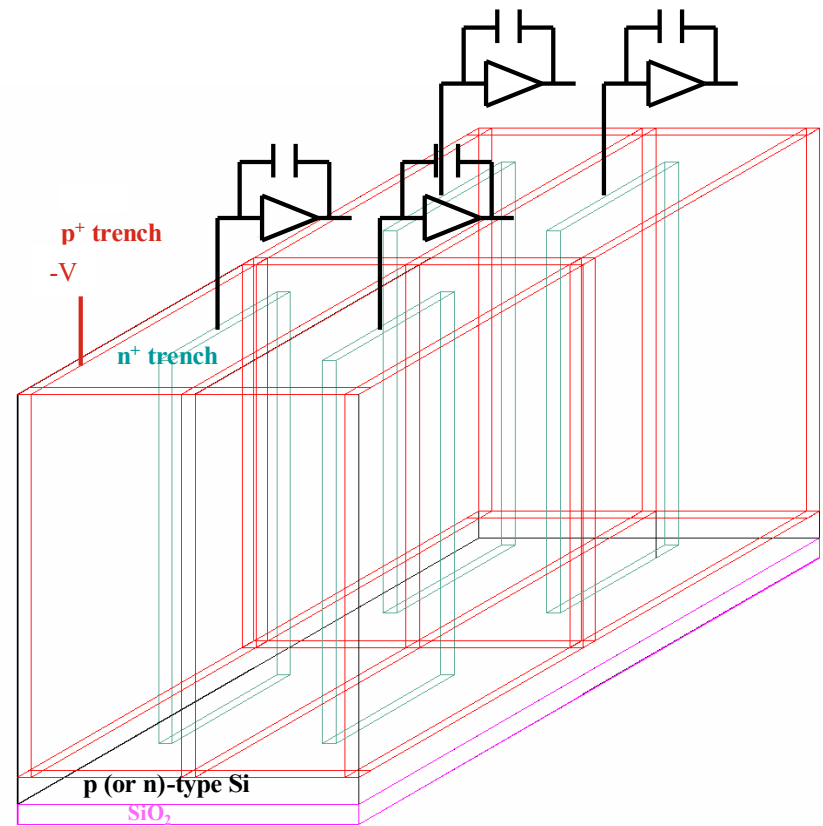
At least one electrode is a trench, each cell is an independent detector

Homogeneous electric field, no saddle point



Concentric type

Electric field with nearly no θ dependence

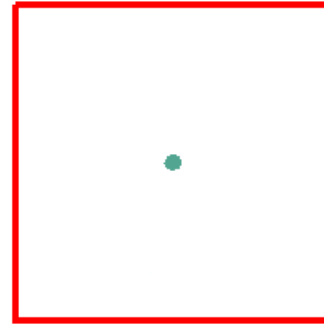
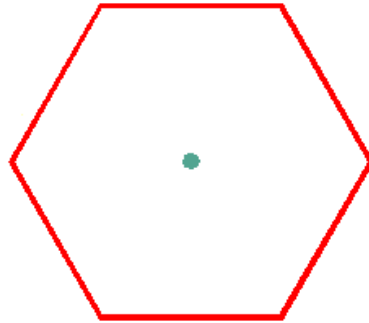
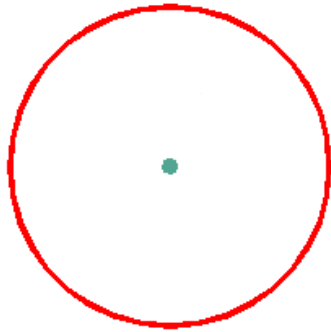


Parallel plate type

Near-linear electric field

Examples of single cells of ICDA

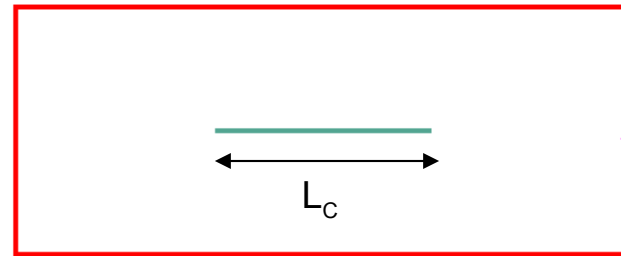
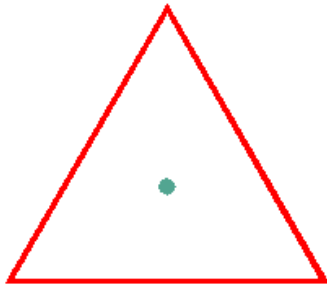
Concentric type:



n (or p) type bulk

—
p⁺ (or n⁺) trench

●
n⁺ (or p⁺) column



L_C ≪ L_T

—
n⁺ (or p⁺) trench

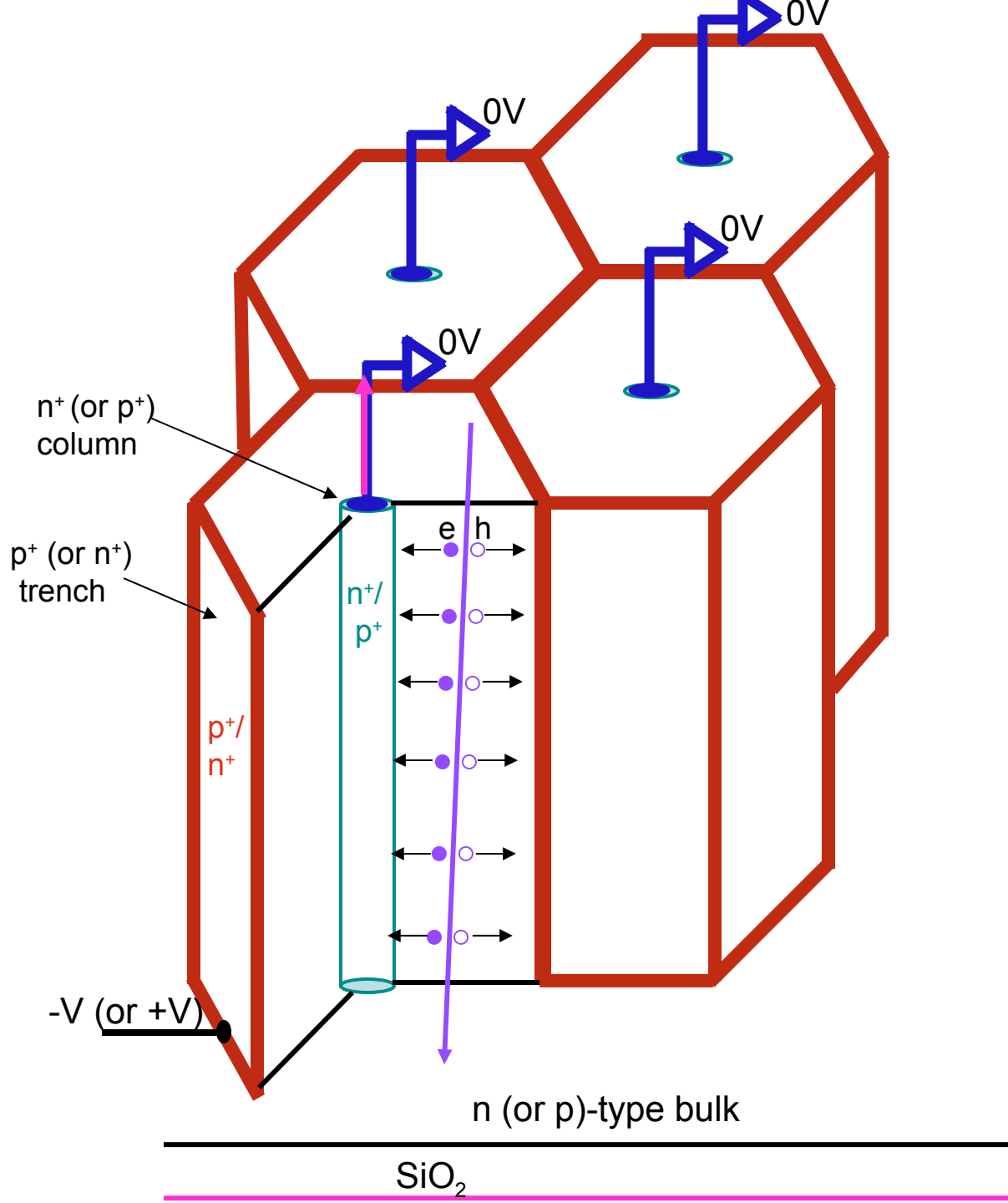
Parallel plate type:

L_C ~ L_T

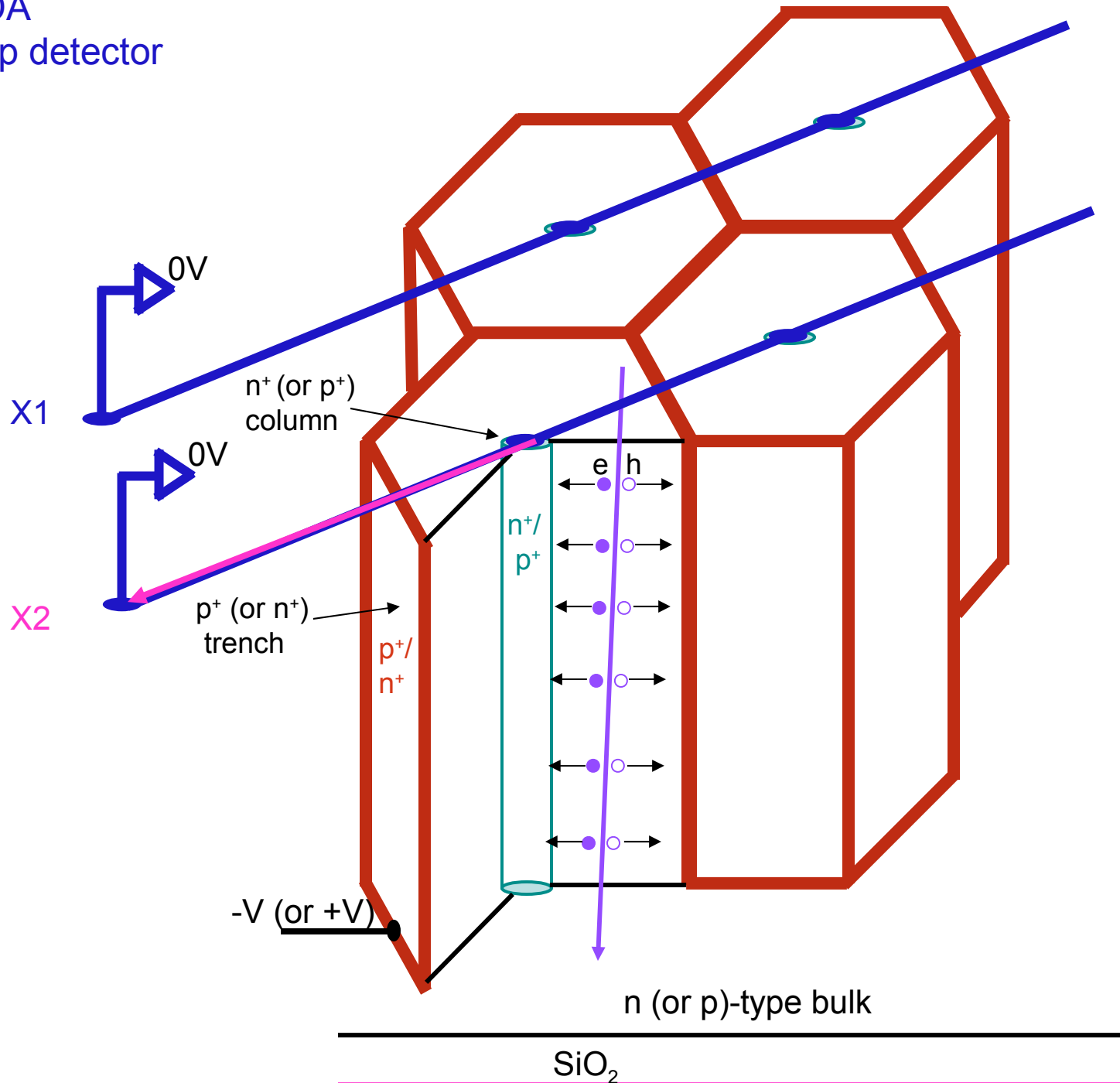


n (or p) type bulk

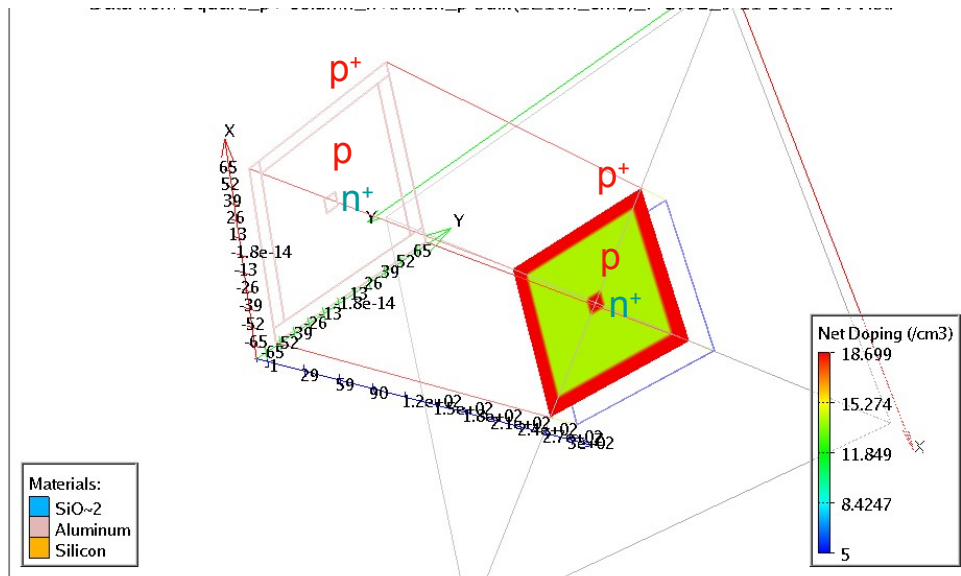
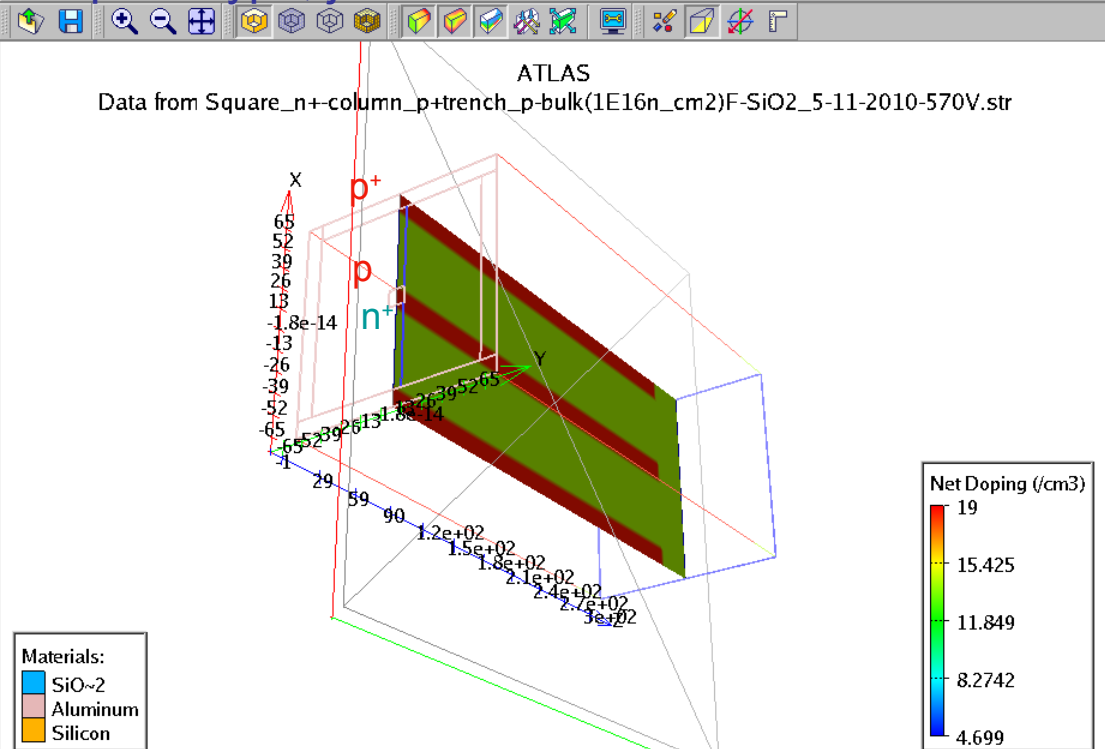
ICDA
Pixel detector

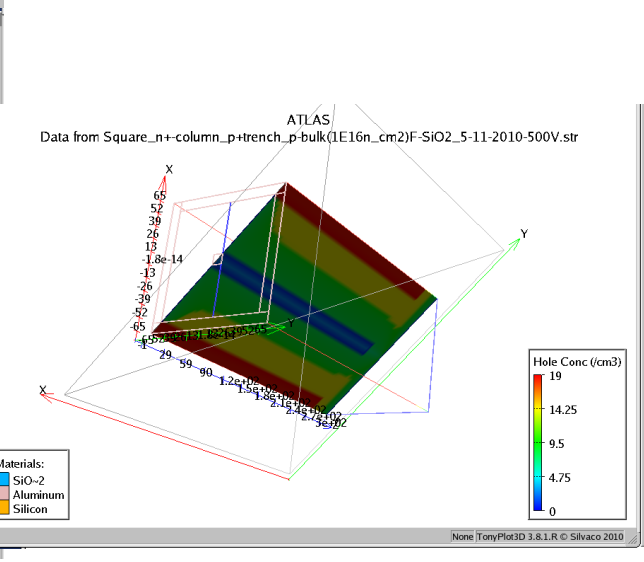
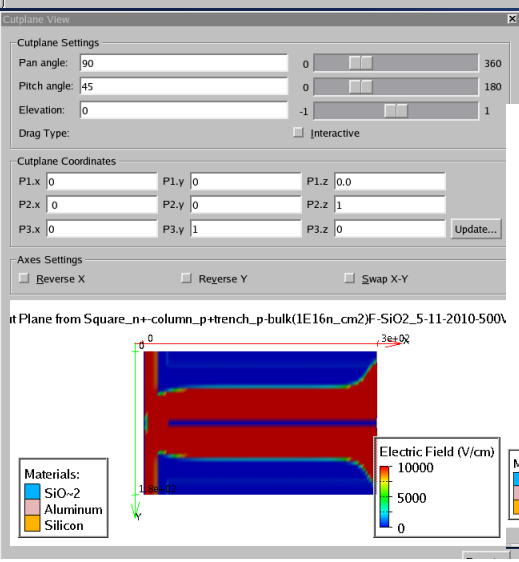
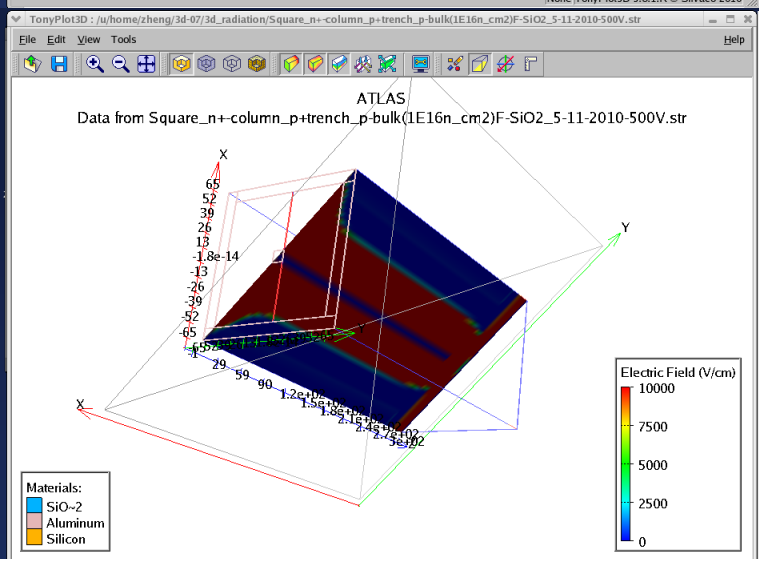
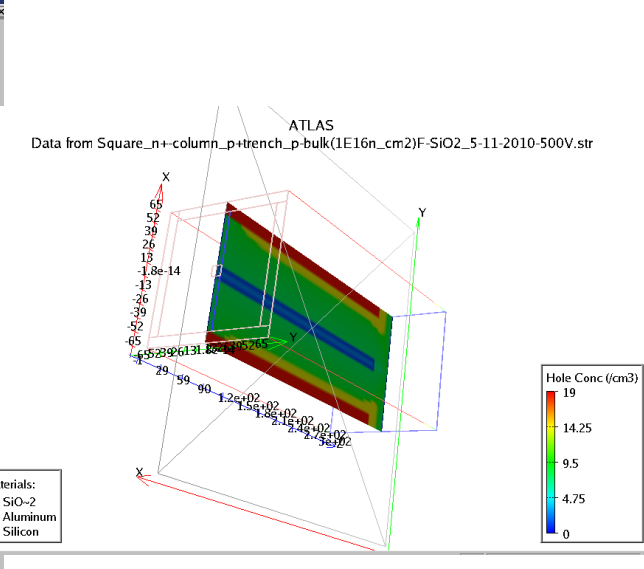
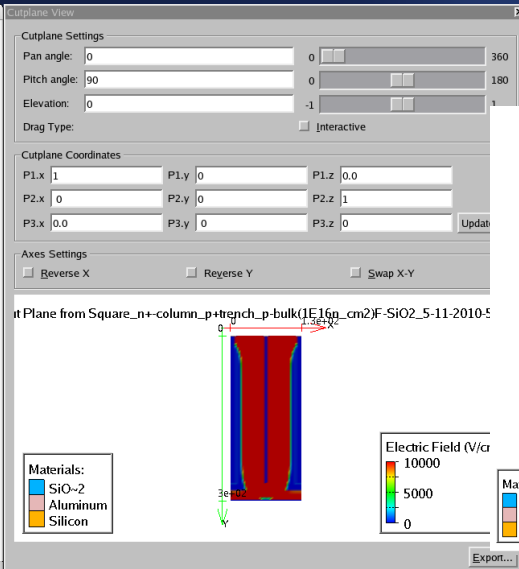
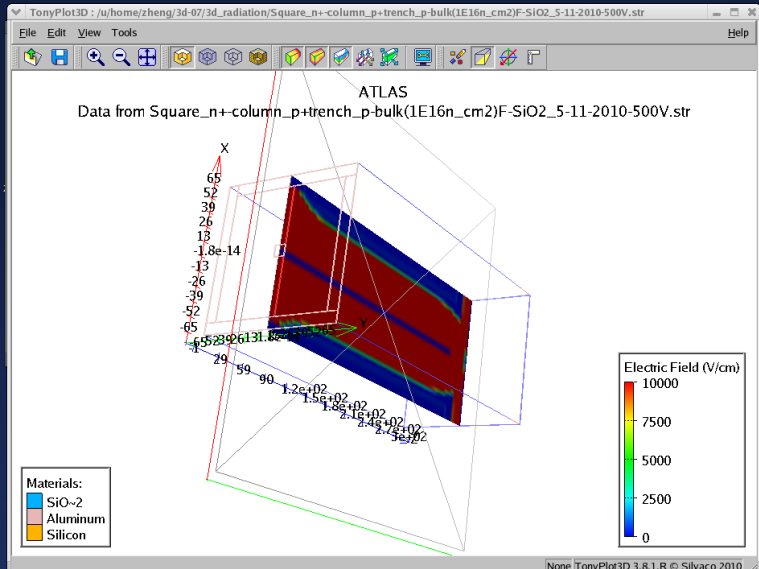


ICDA Strip detector

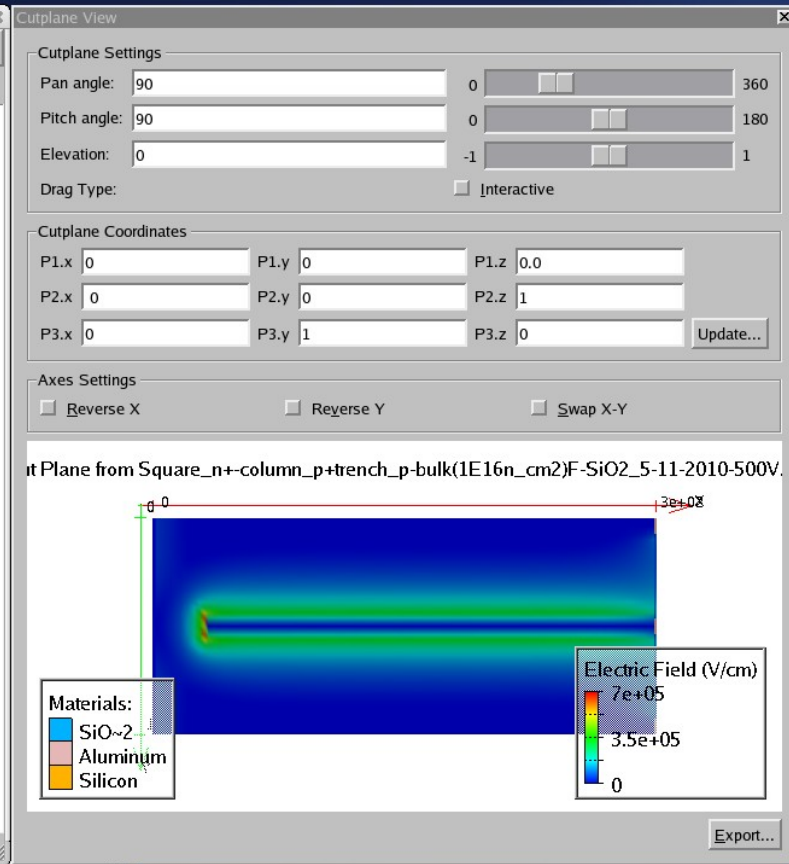
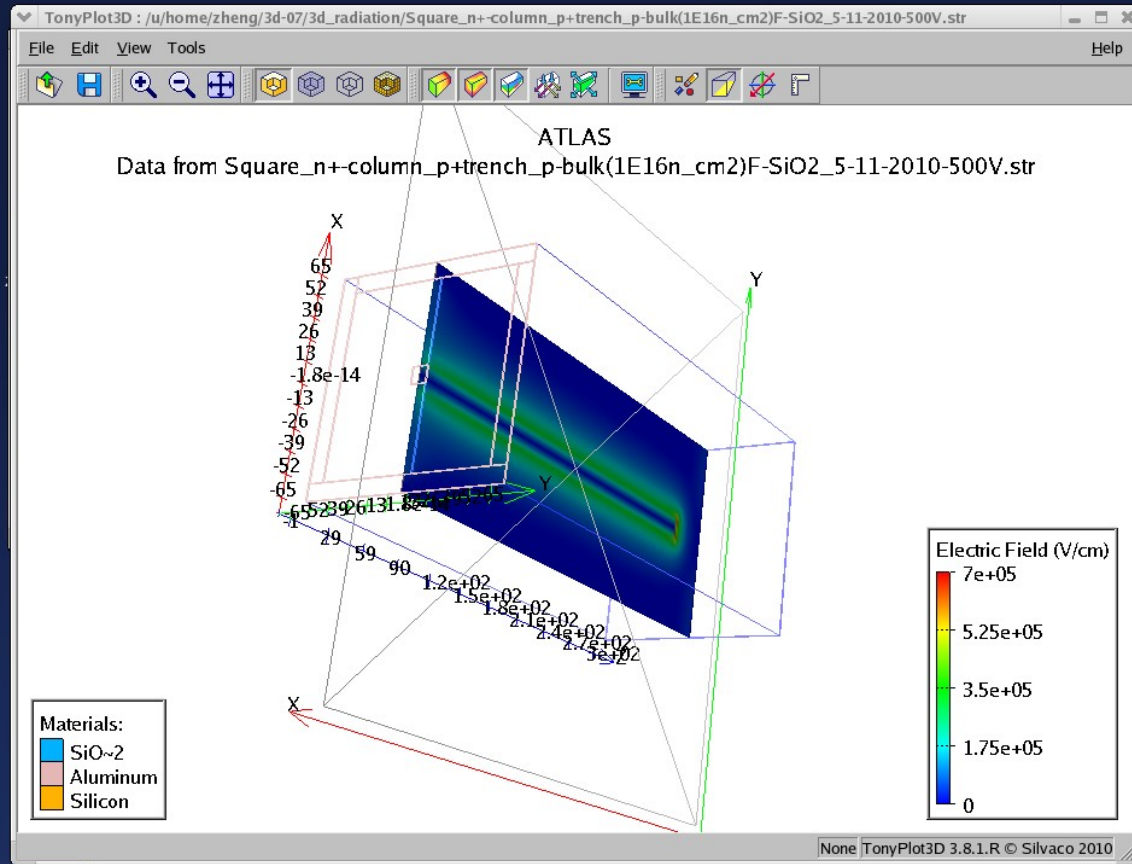


Square-type, junction on the n⁺ center column



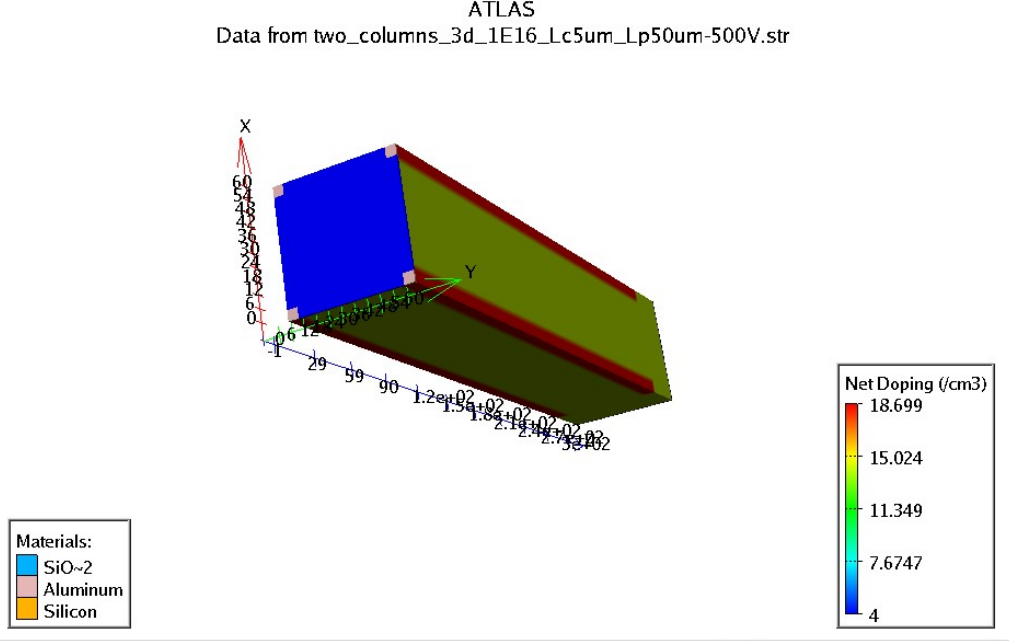
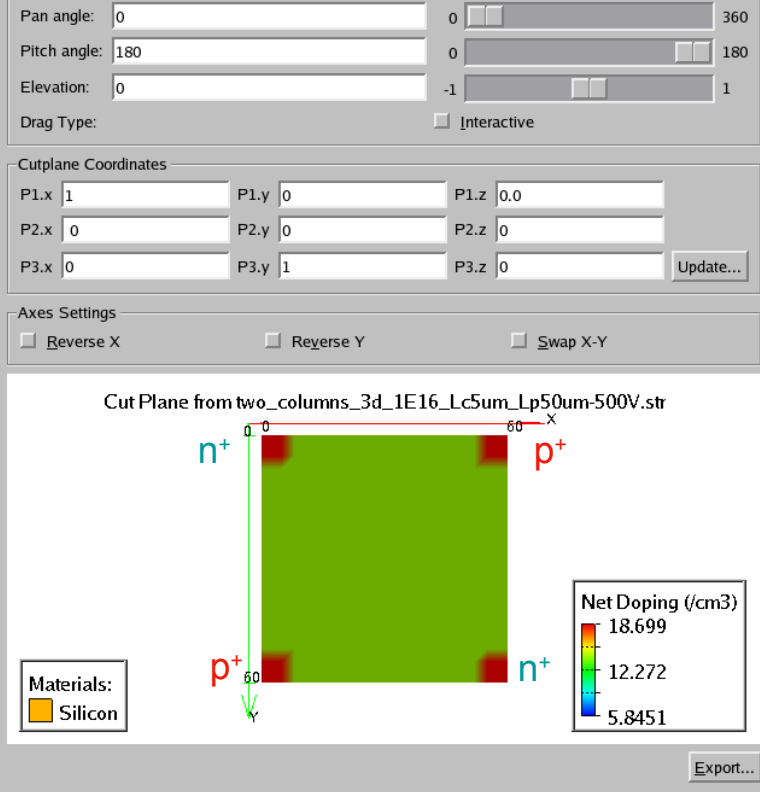
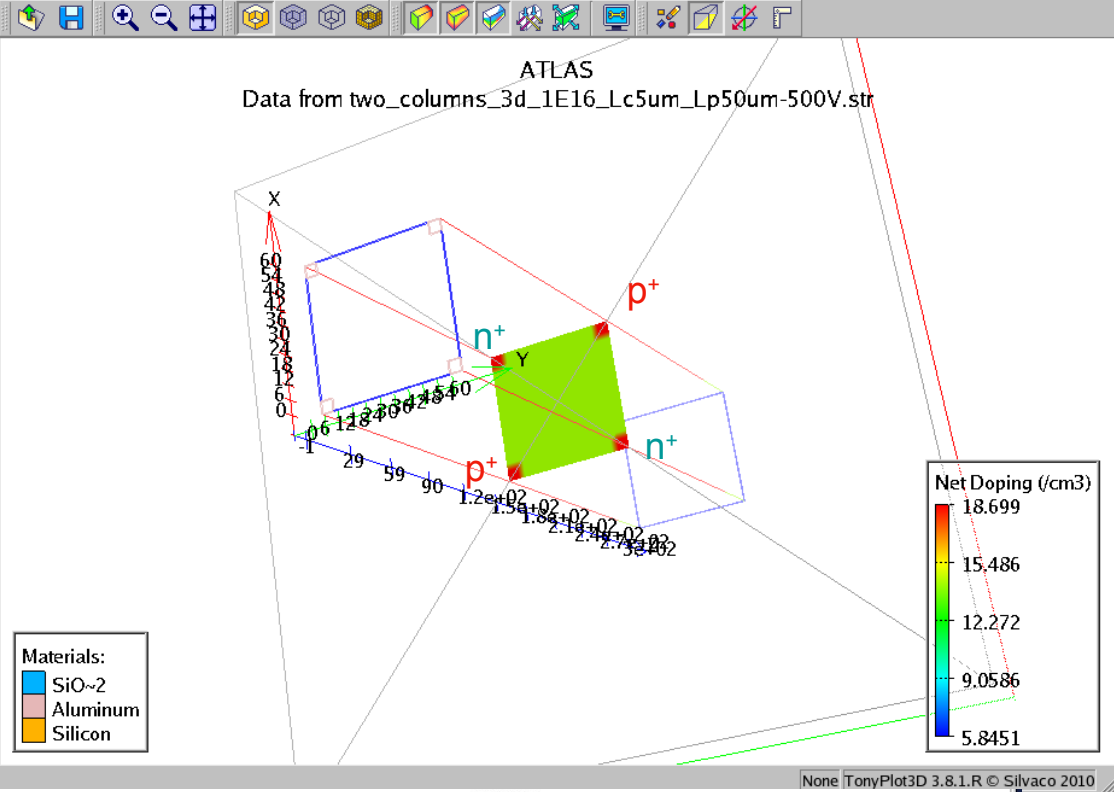


Homogeneous electric field
 E-field even under the trench and column --- good for sensitivity under
 E-field and hole concentration on the center column, $1 \times 10^{16} n_{eq}/\text{cm}^2$, 500 V.

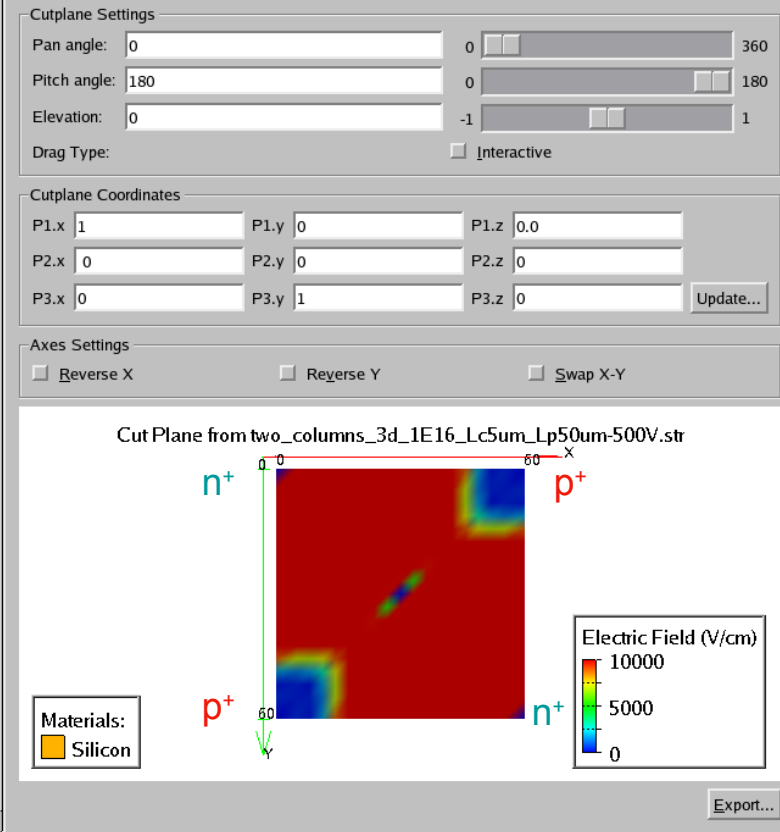
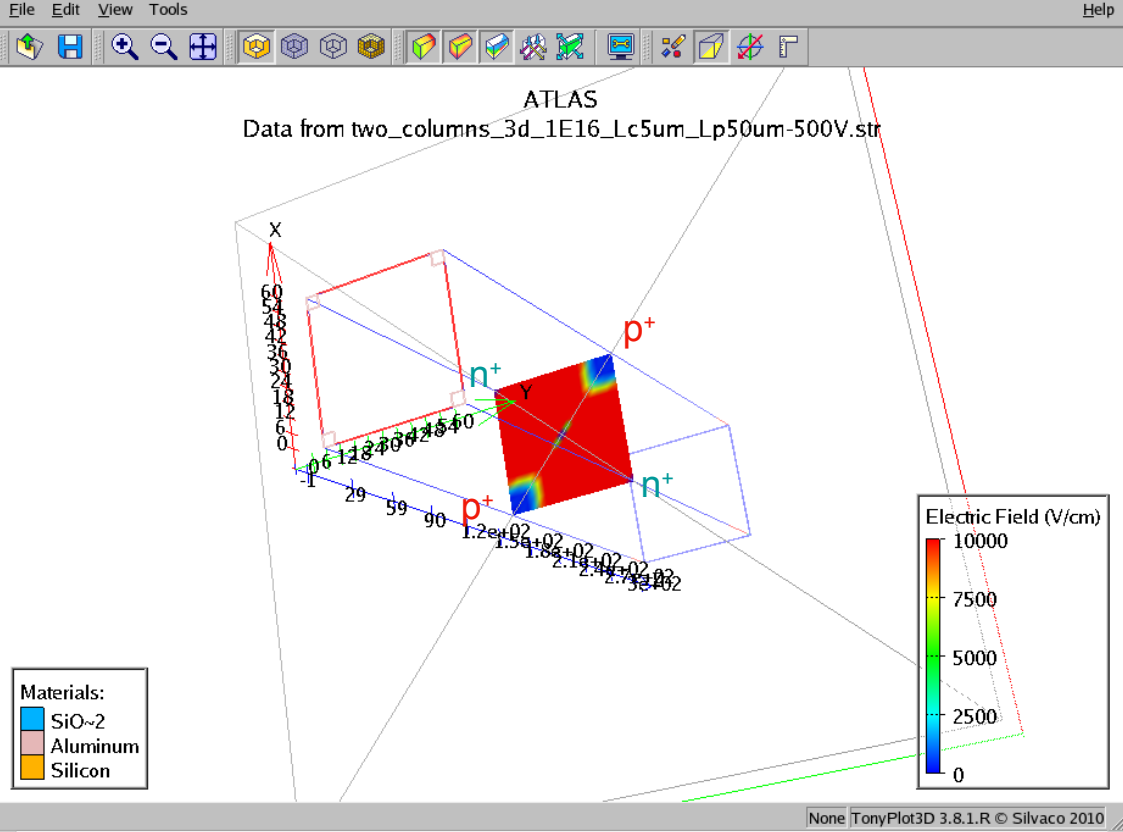


The highest E-field is under the junction column
 >700 kV/cm

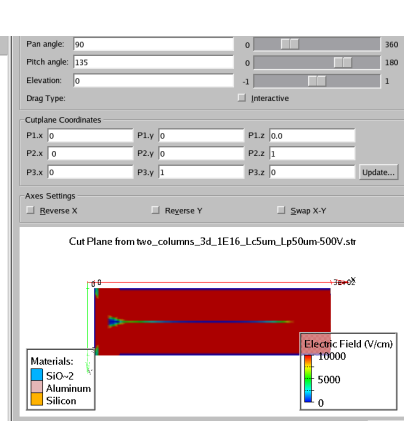
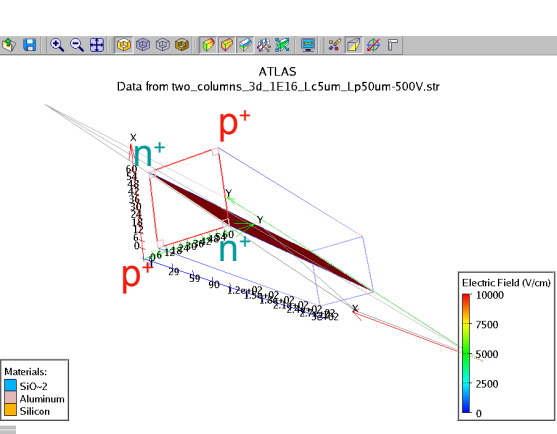
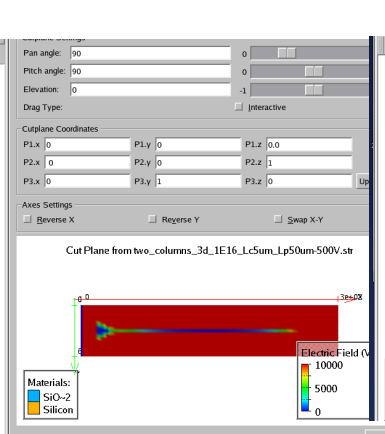
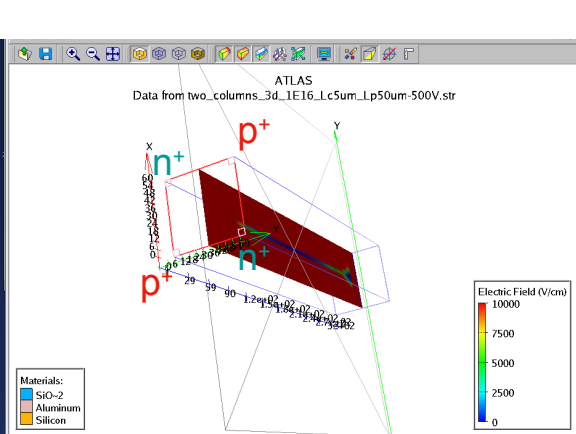
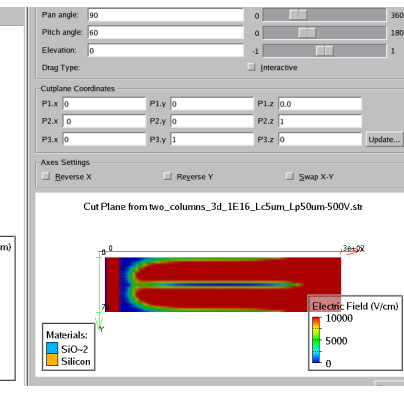
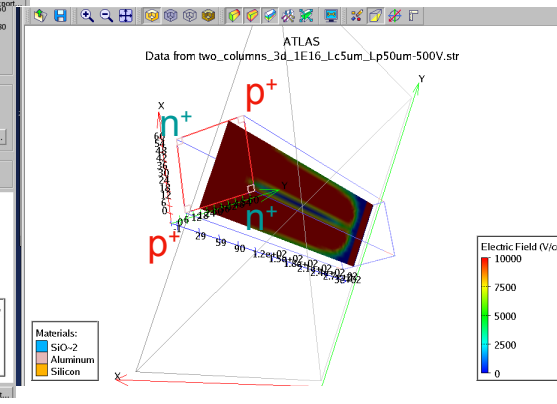
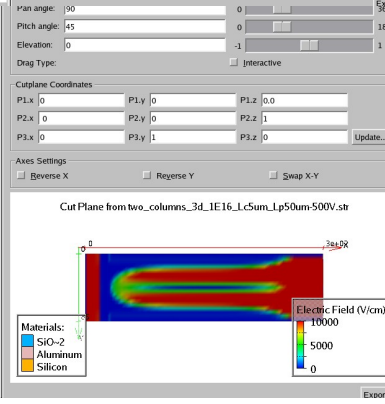
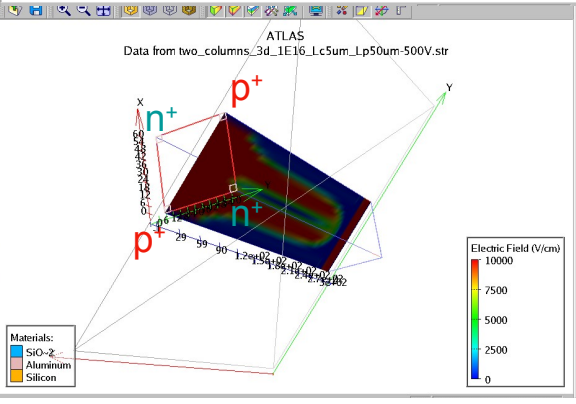
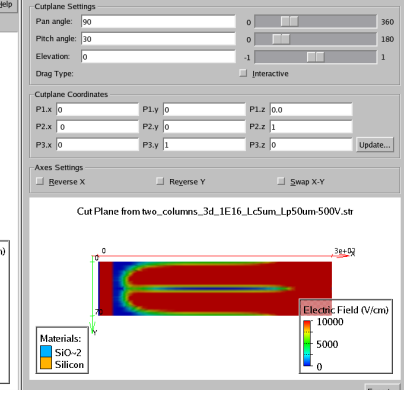
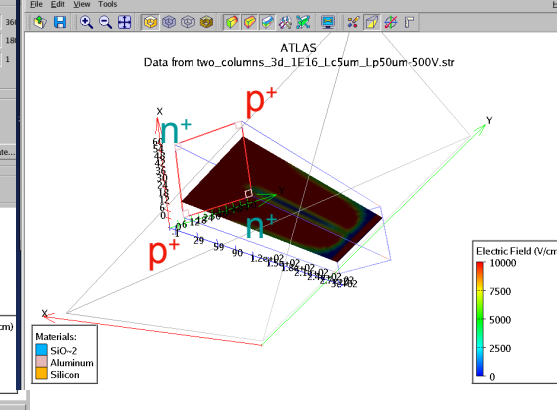
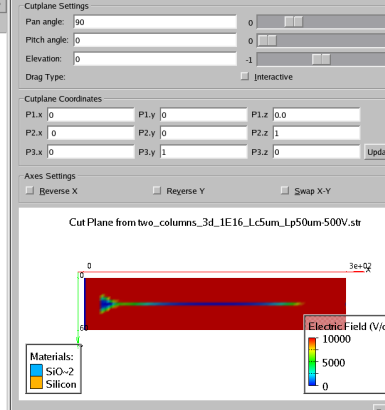
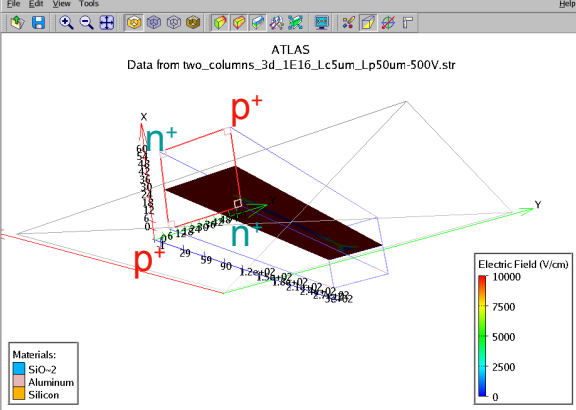
E-field, junction on the center column, $1 \times 10^{16} \text{ n}_{\text{eq}}/\text{cm}^2$, 500 V.



Standard (STD) BNL 2C-3D detector

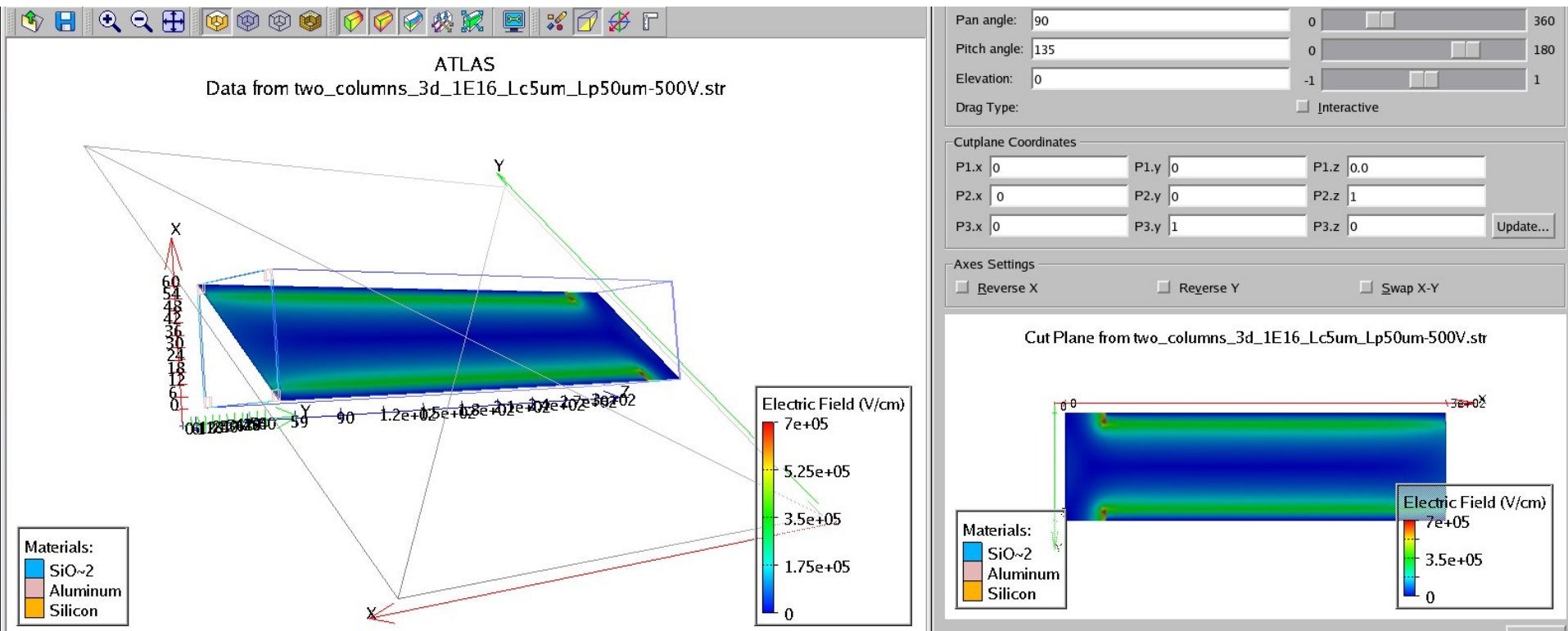


No/low field at saddle points



Very non-homogeneous electric field, no/low field at saddle points

E-field, STD BNL 2C-3D detector column, $1 \times 10^{16} n_{eq}/cm^2$, 500 V.

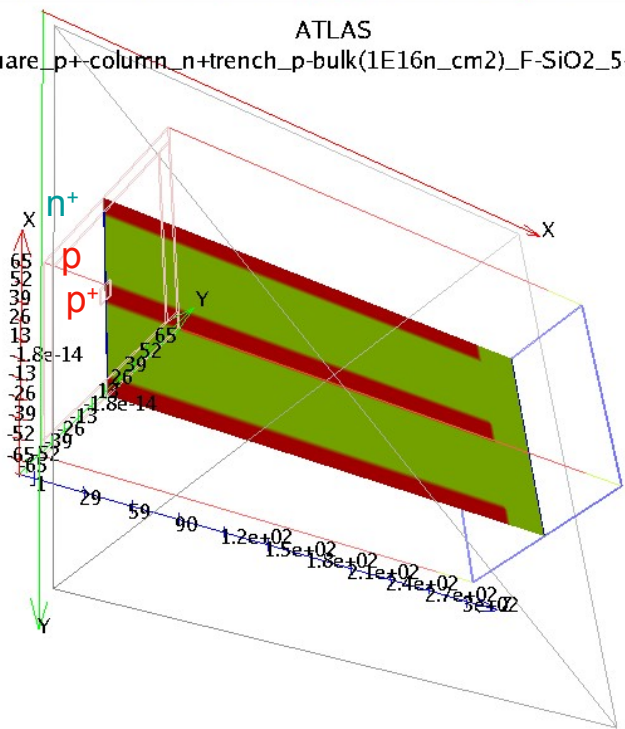


The highest E-field is under the n⁺ junction columns
>700 kV/cm

E-field, STD BNL 2C-3D detector column, $1 \times 10^{16} n_{eq}/\text{cm}^2$, 500 V.

Square-type, junction on the n⁺ trench

ATLAS
Data from Square_p+-column_n+trench_p-bulk(1E16n_cm2)_F-SiO2_5-11-2010-240V.str



Pitch angle: 90 0 180
Elevation: 0 -1 1
Drag Type: Interactive

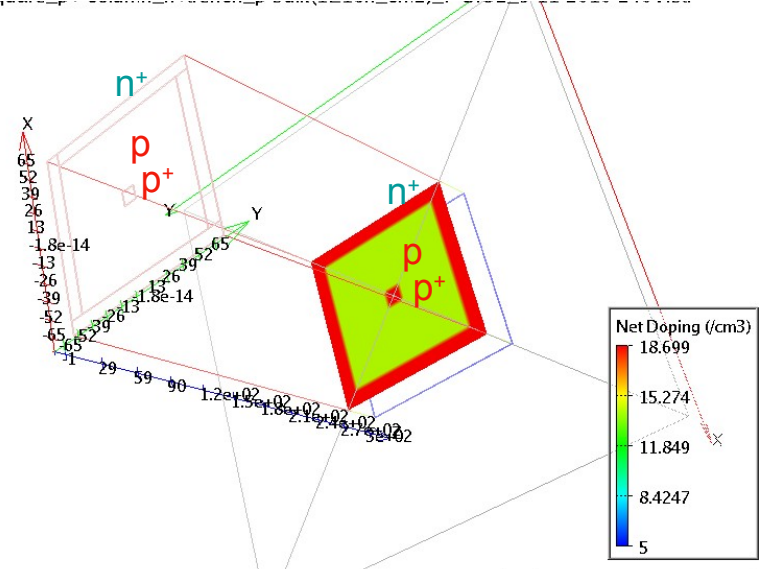
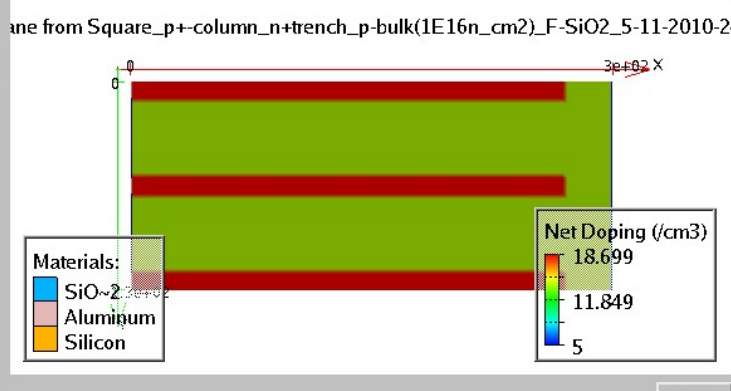
Cutplane Coordinates

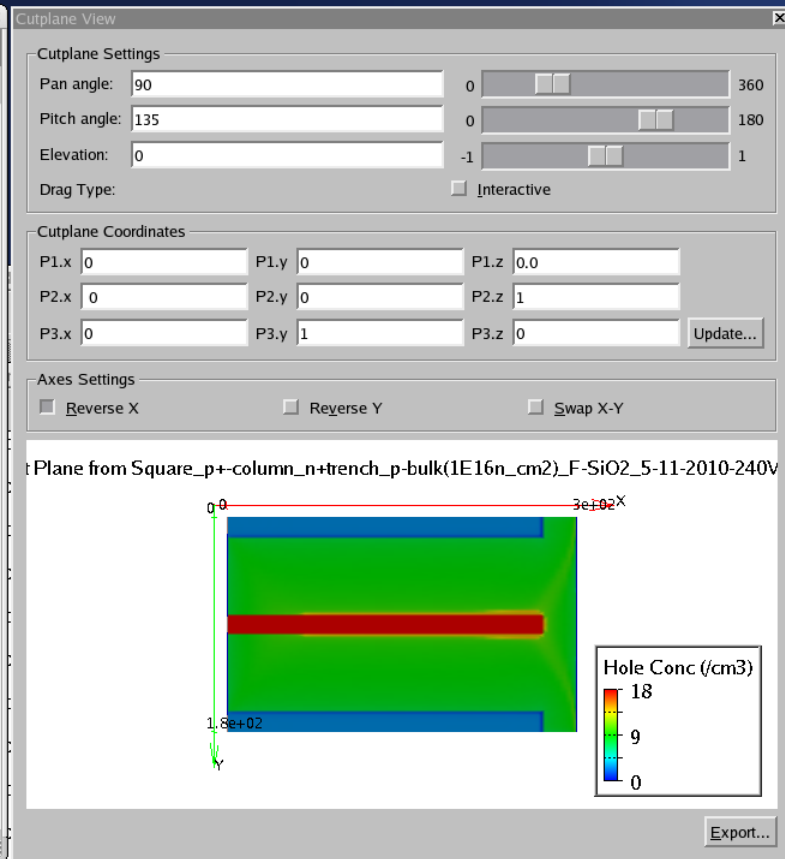
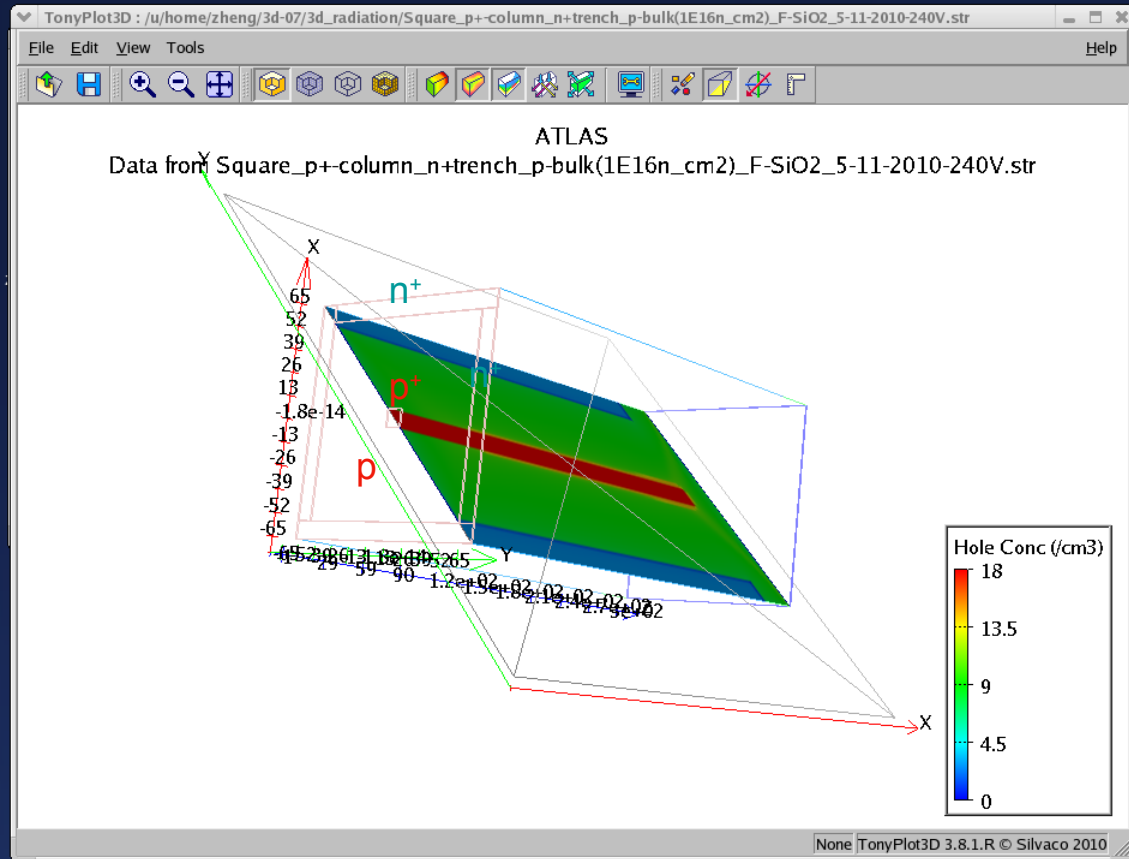
P1.x	0	P1.y	0.0	P1.z	0.0
P2.x	0	P2.y	1	P2.z	0
P3.x	0	P3.y	0	P3.z	1

Update...

Axes Settings

Reverse X Reverse Y Swap X-Y



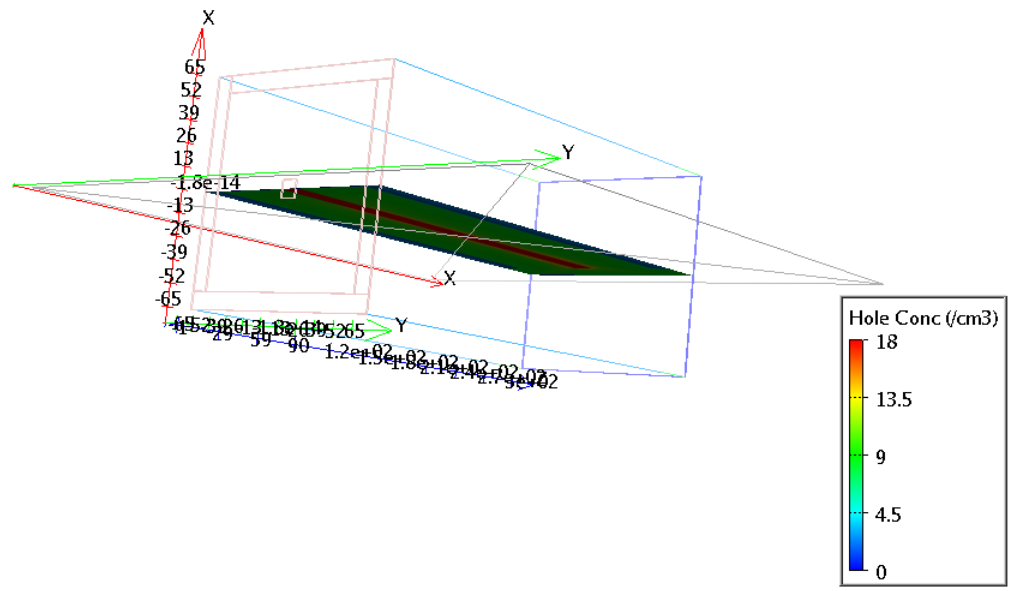


The hole concentration for non-depleted Si is $2 \times 10^{14} / \text{cm}^3$

The whole cell is fully depleted at 240 V
even < the value of 400 V for 2D planar detector!



ATLAS
Data from Square_p+column_n+trench_p-bulk(1E16n_cm2)_F-SiO2_5-11-2010-240V.str



Cutplane Settings

Pan angle: 90 0 360

Pitch angle: 0 0 180

Elevation: 0 -1 1

Drag Type: Interactive

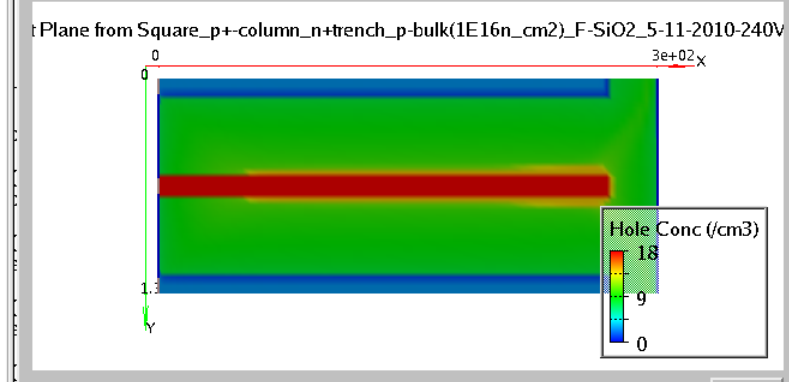
Cutplane Coordinates

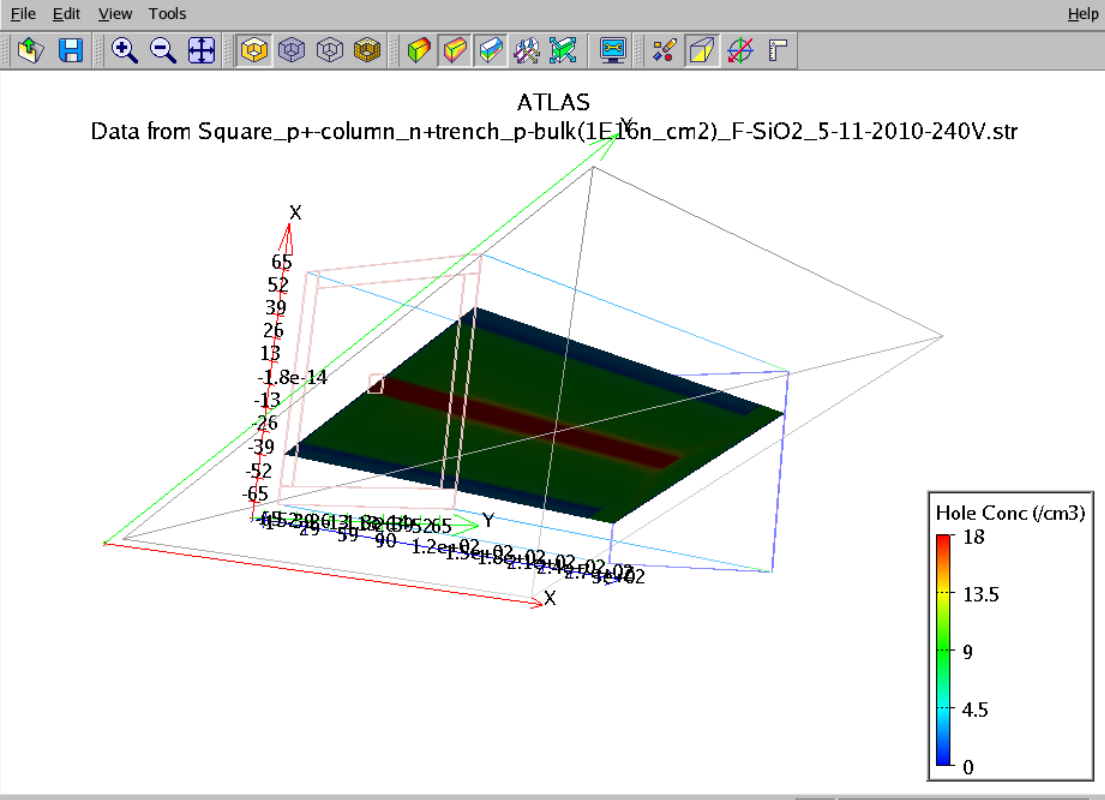
P1.x	0	P1.y	0	P1.z	0.0
P2.x	0	P2.y	0	P2.z	1
P3.x	0	P3.y	1	P3.z	0

Update...

Axes Settings

Reverse X Reverse Y Swap X-Y





Cutplane Settings

Pan angle: 90 0 360

Pitch angle: 30 0 180

Elevation: 0 -1 1

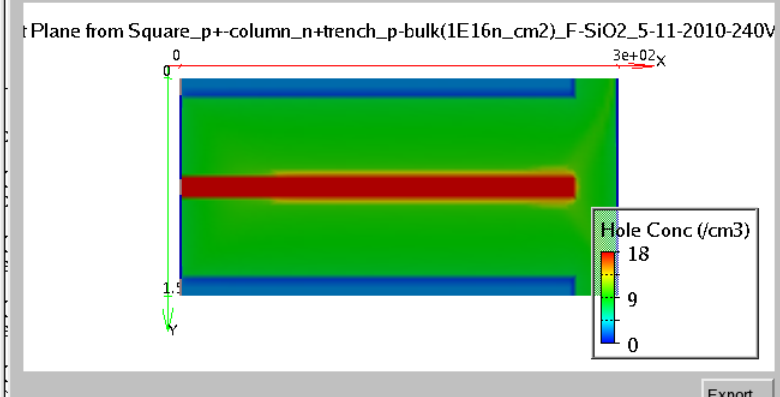
Drag Type: Interactive

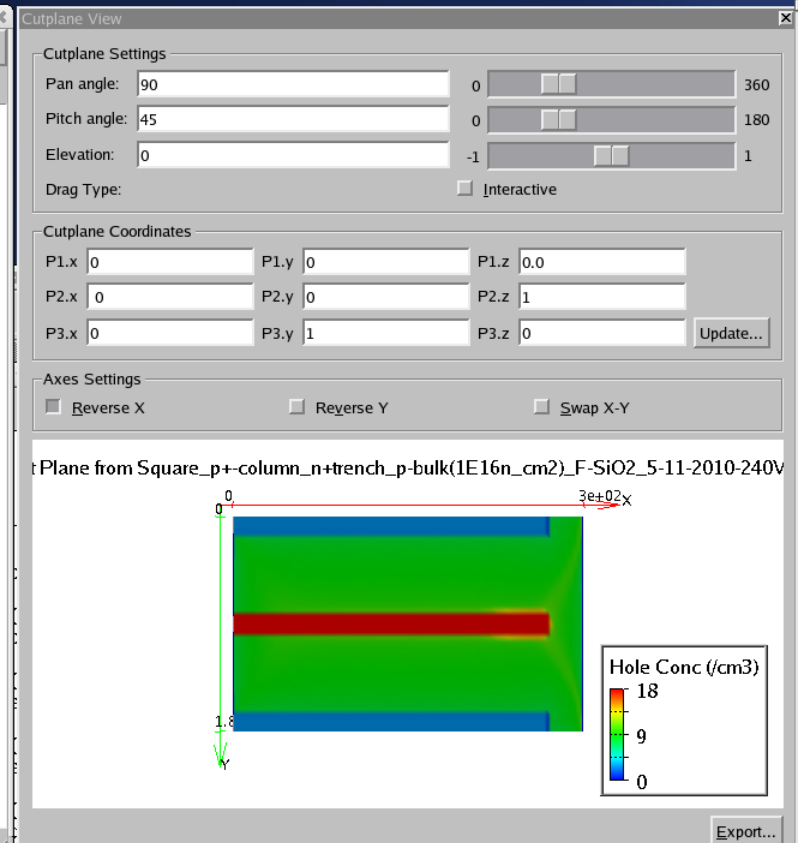
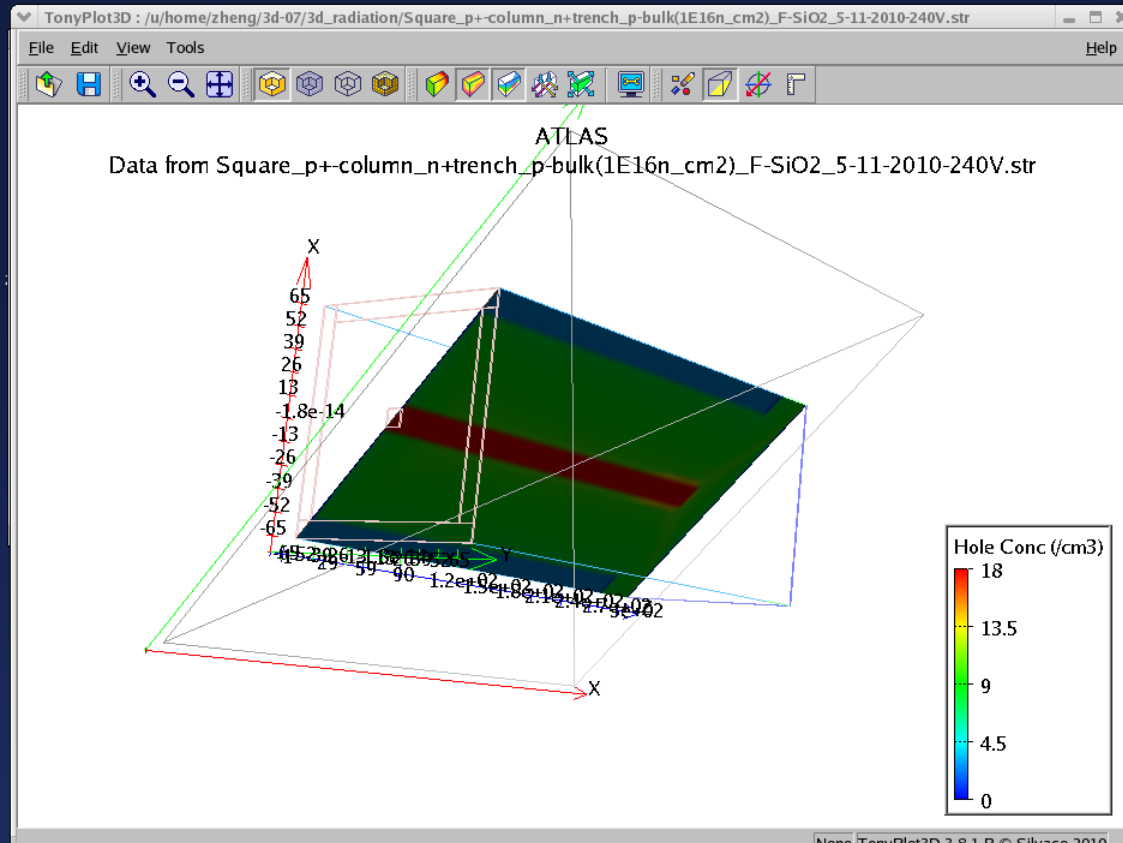
Cutplane Coordinates

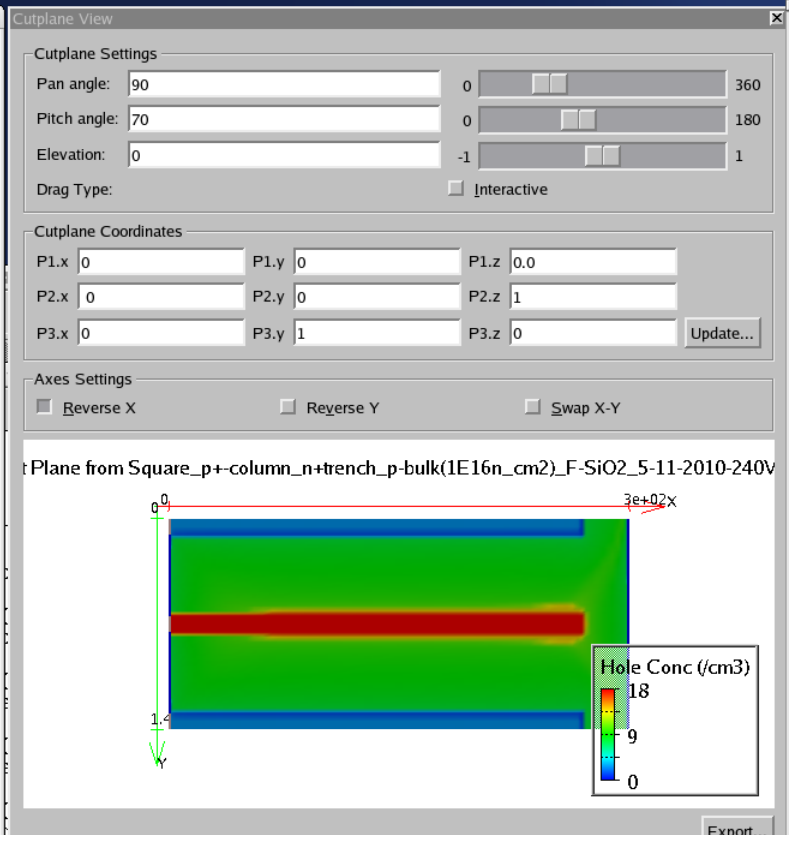
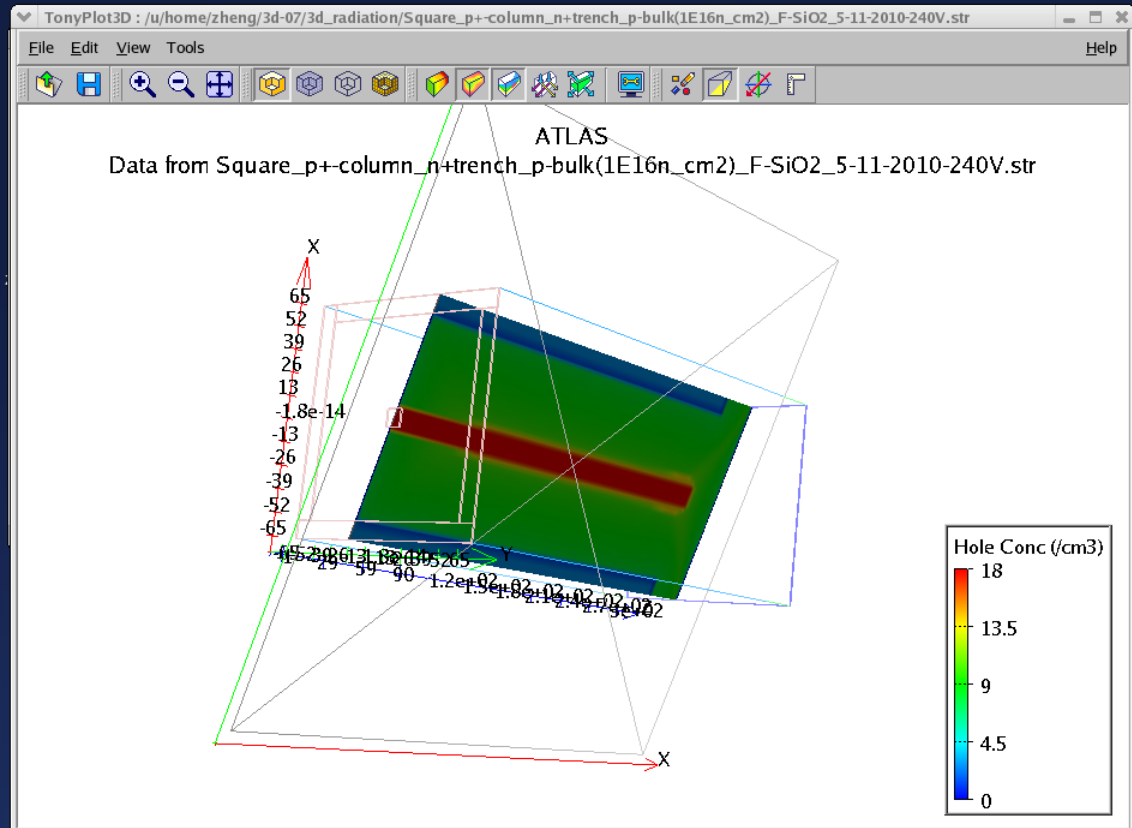
P1.x	0	P1.y	0	P1.z	0.0
P2.x	0	P2.y	0	P2.z	1
P3.x	0	P3.y	1	P3.z	0

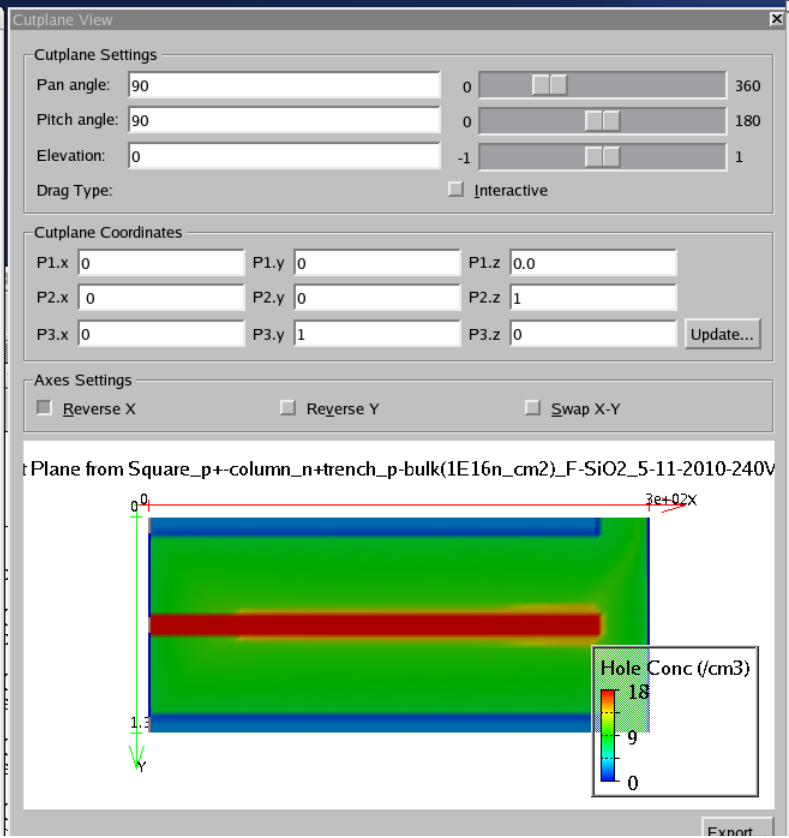
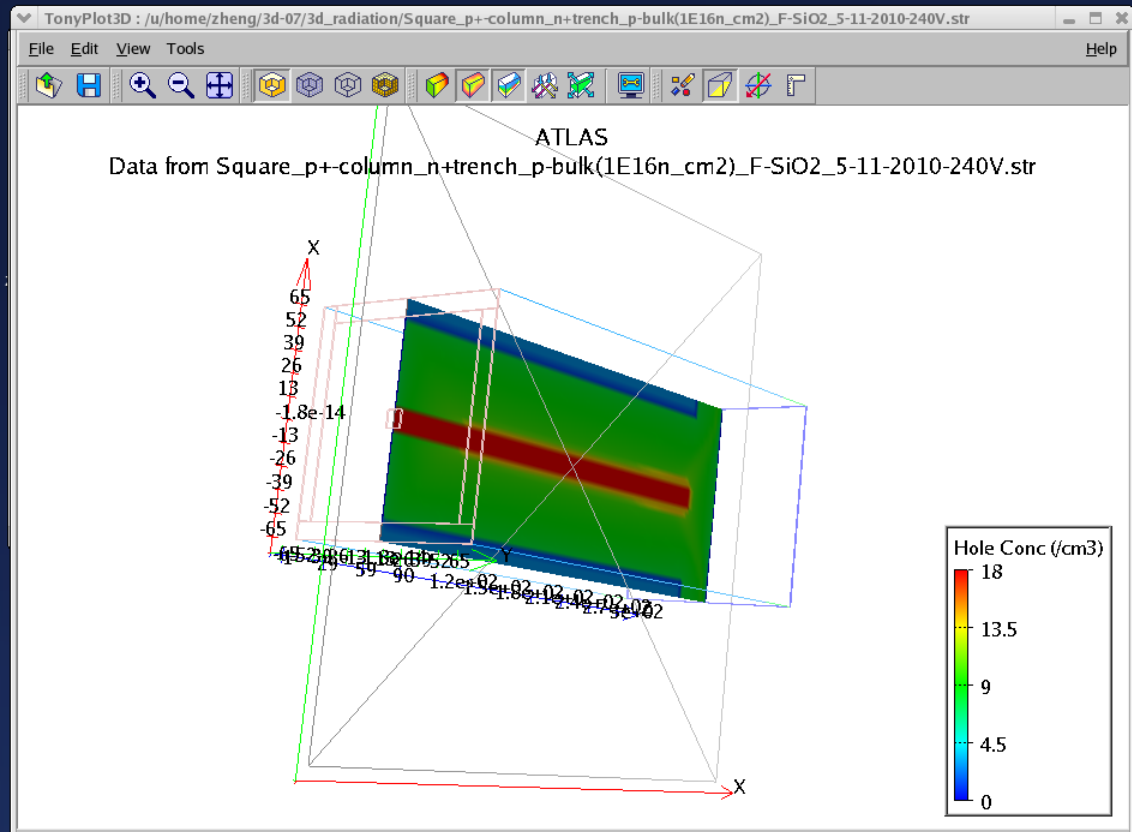
Axes Settings

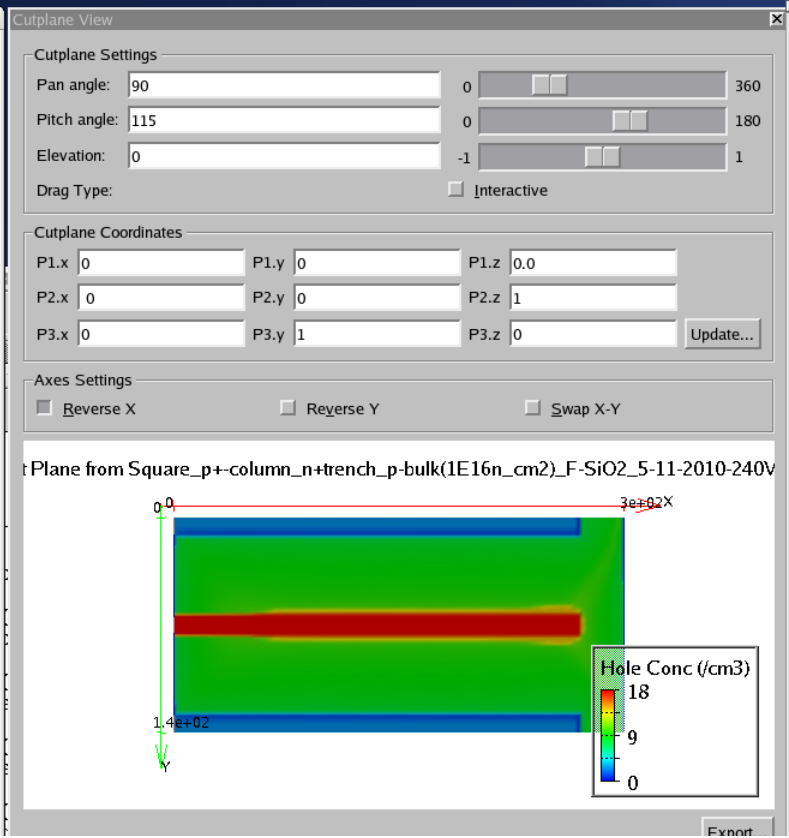
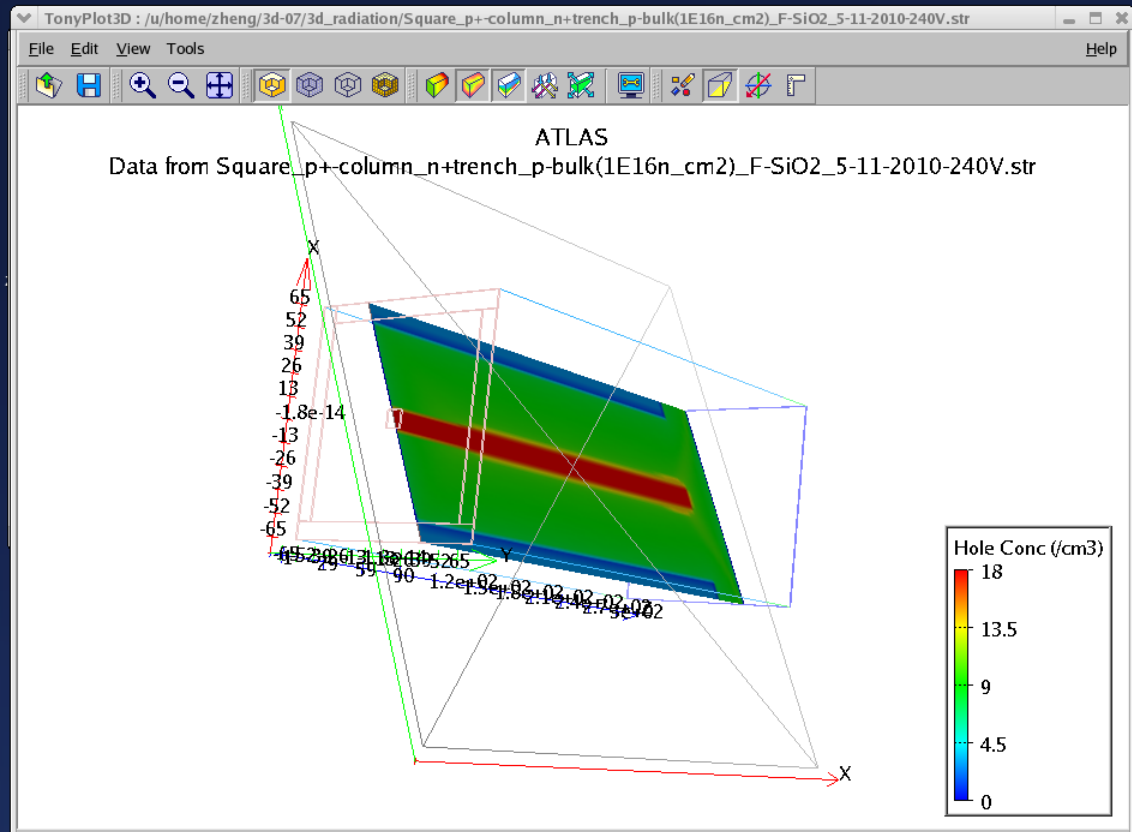
Reverse X Reverse Y Swap X-Y

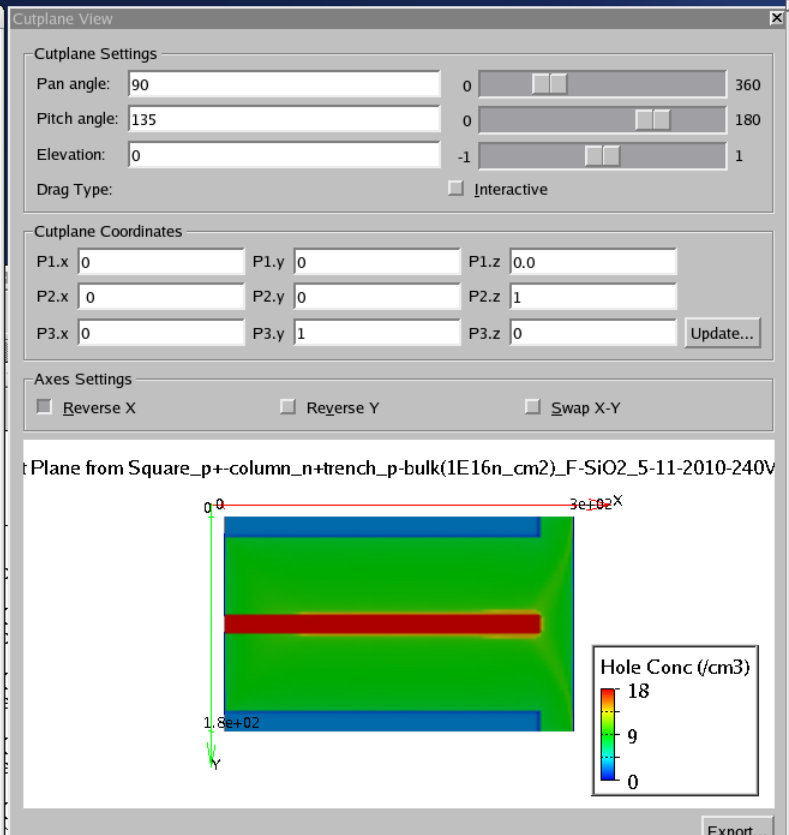
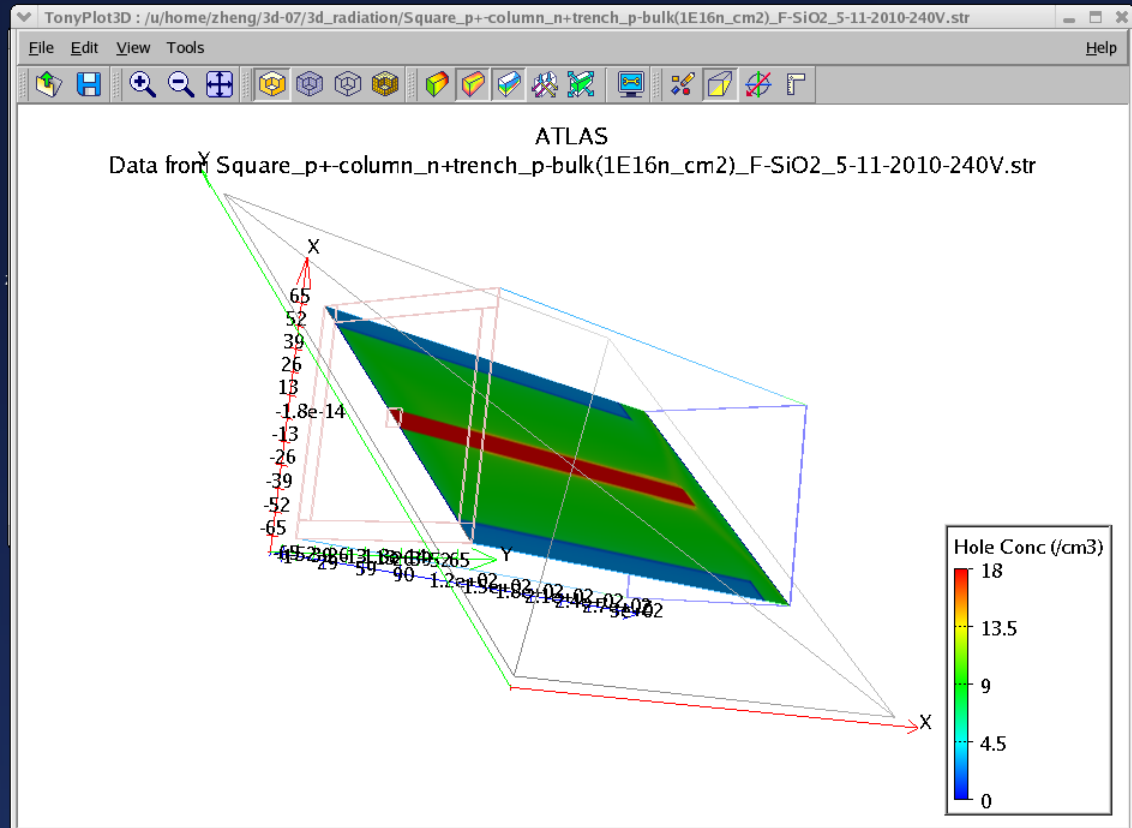


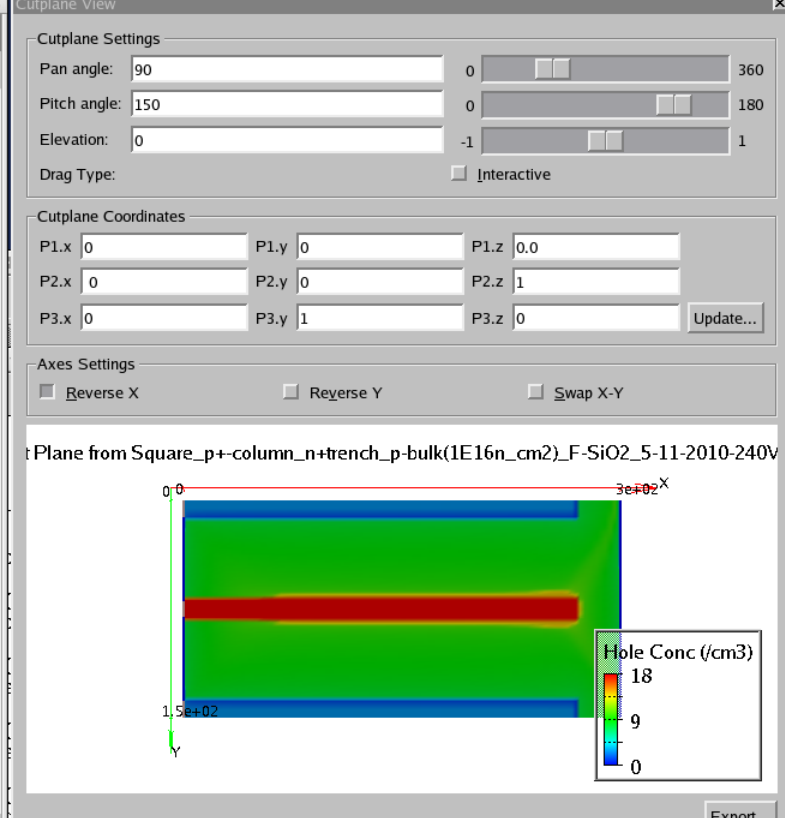
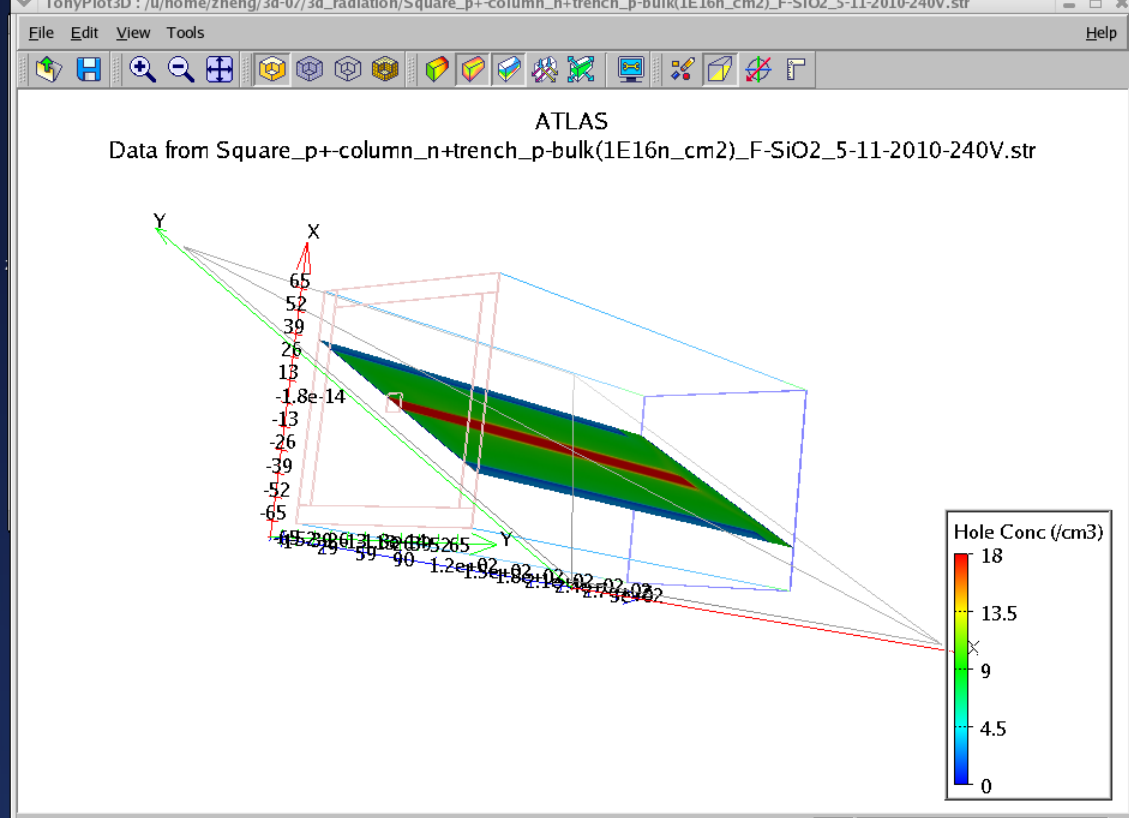


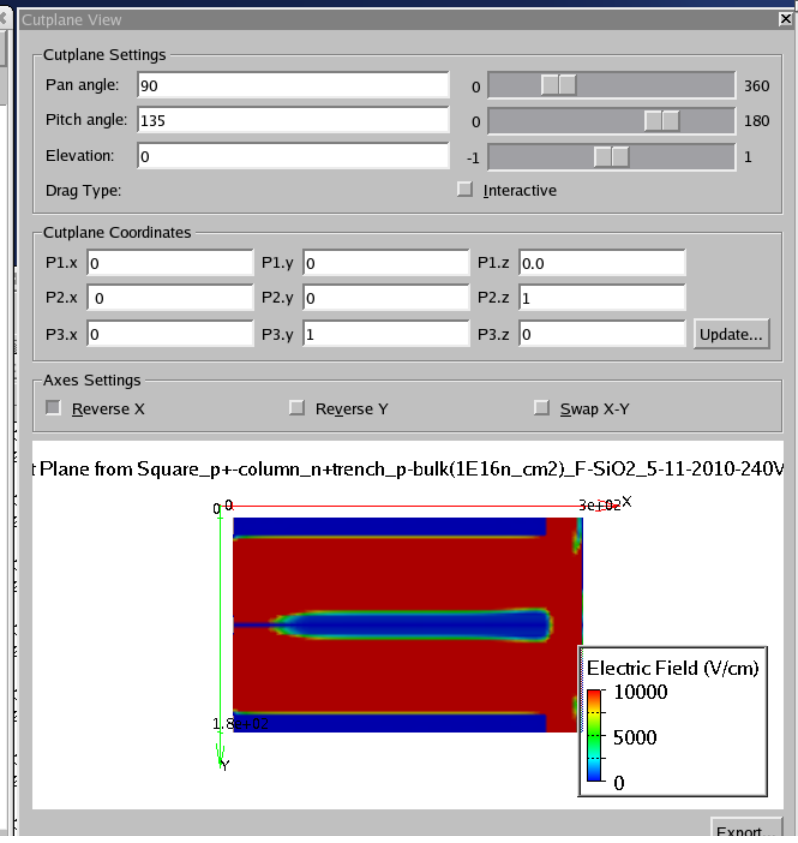
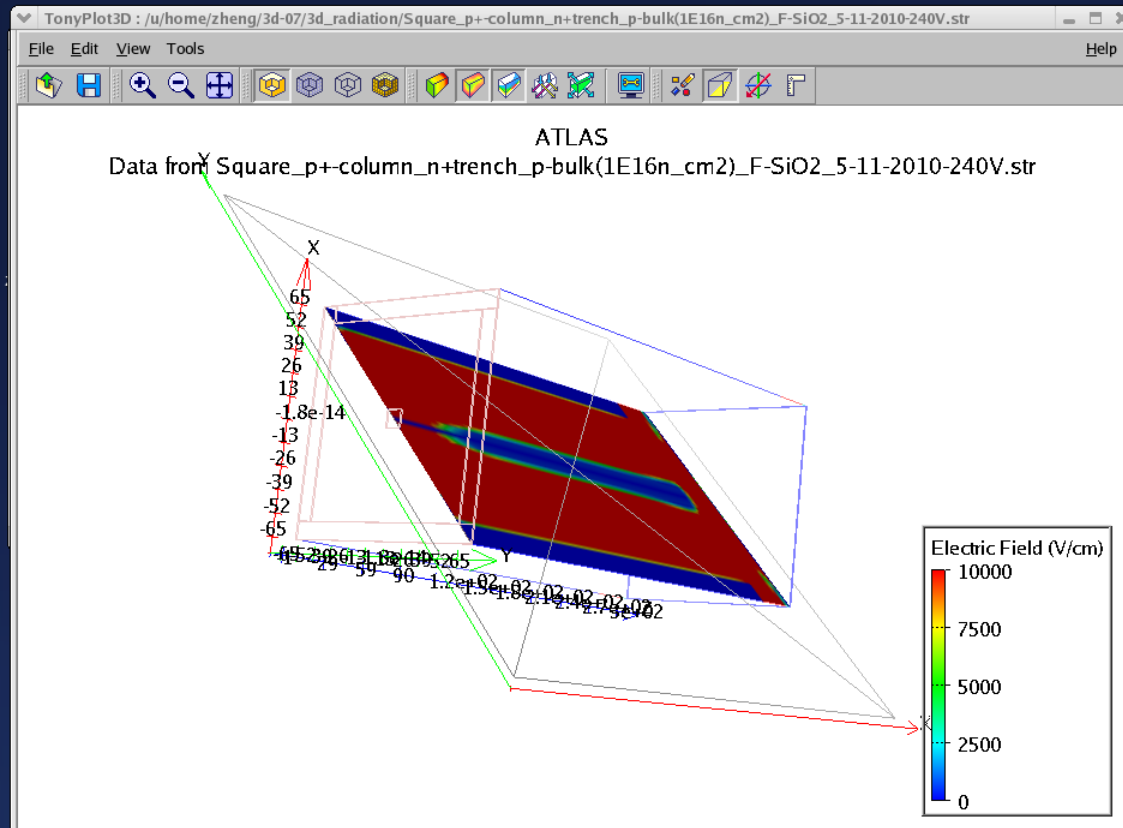


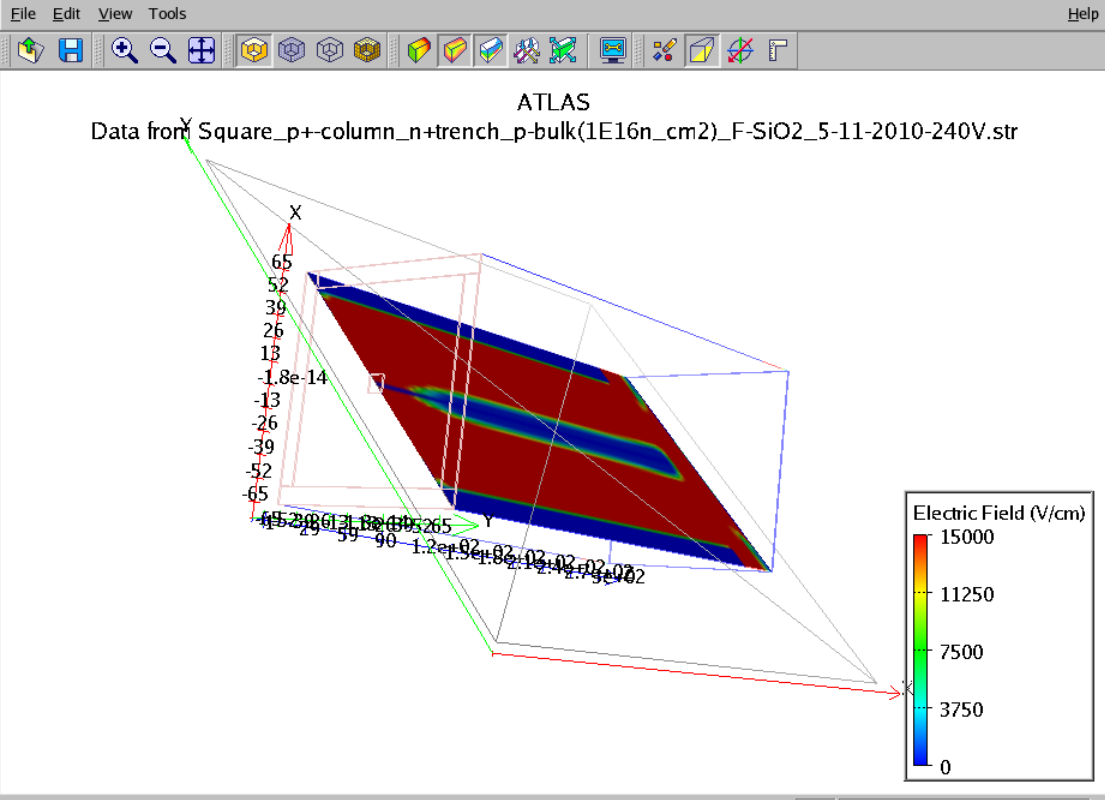












Cutplane Settings

Pan angle: 90 0 360

Pitch angle: 135 0 180

Elevation: 0 -1 1

Drag Type: Interactive

Cutplane Coordinates

P1.x 0 P1.y 0 P1.z 0.0

P2.x 0 P2.y 0 P2.z 1

P3.x 0 P3.y 1 P3.z 0

Axes Settings

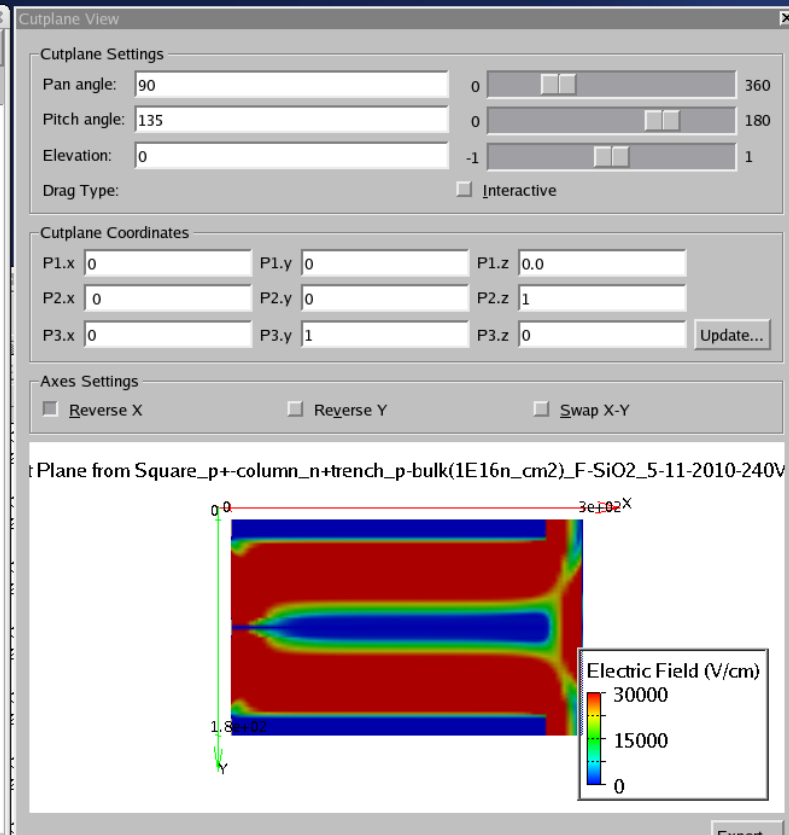
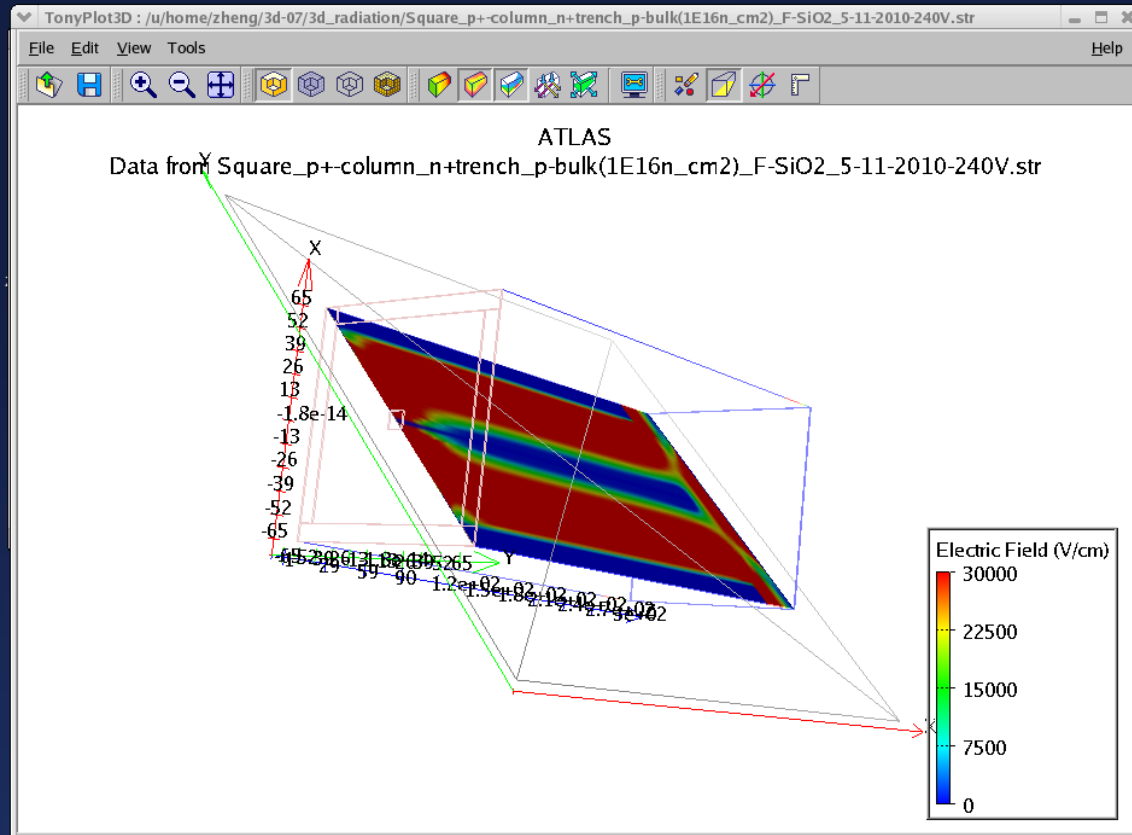
Reverse X Reverse Y Swap X-Y

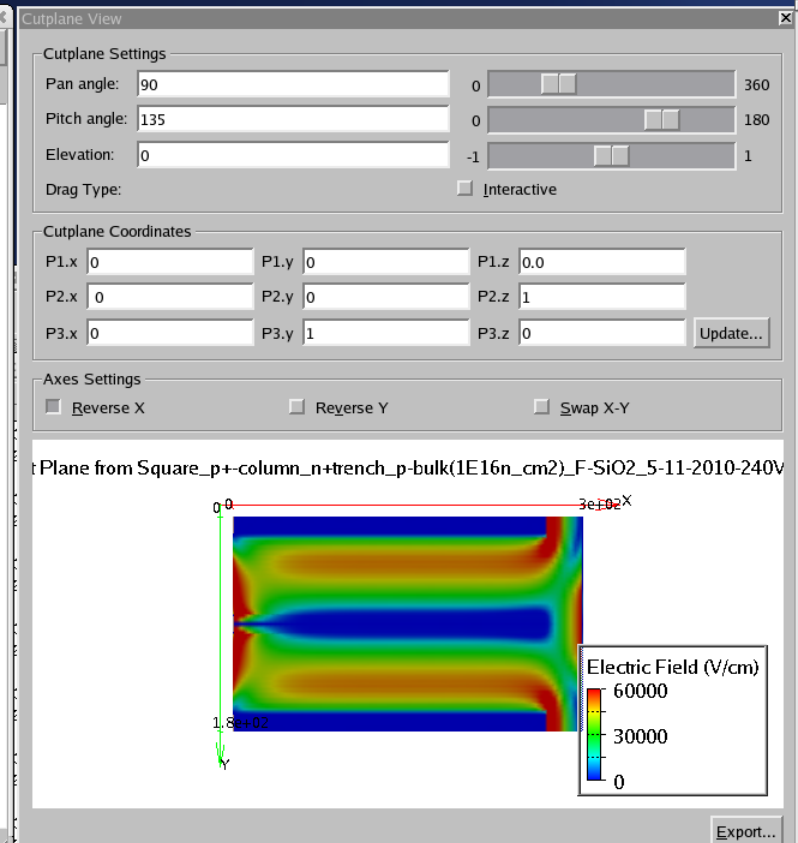
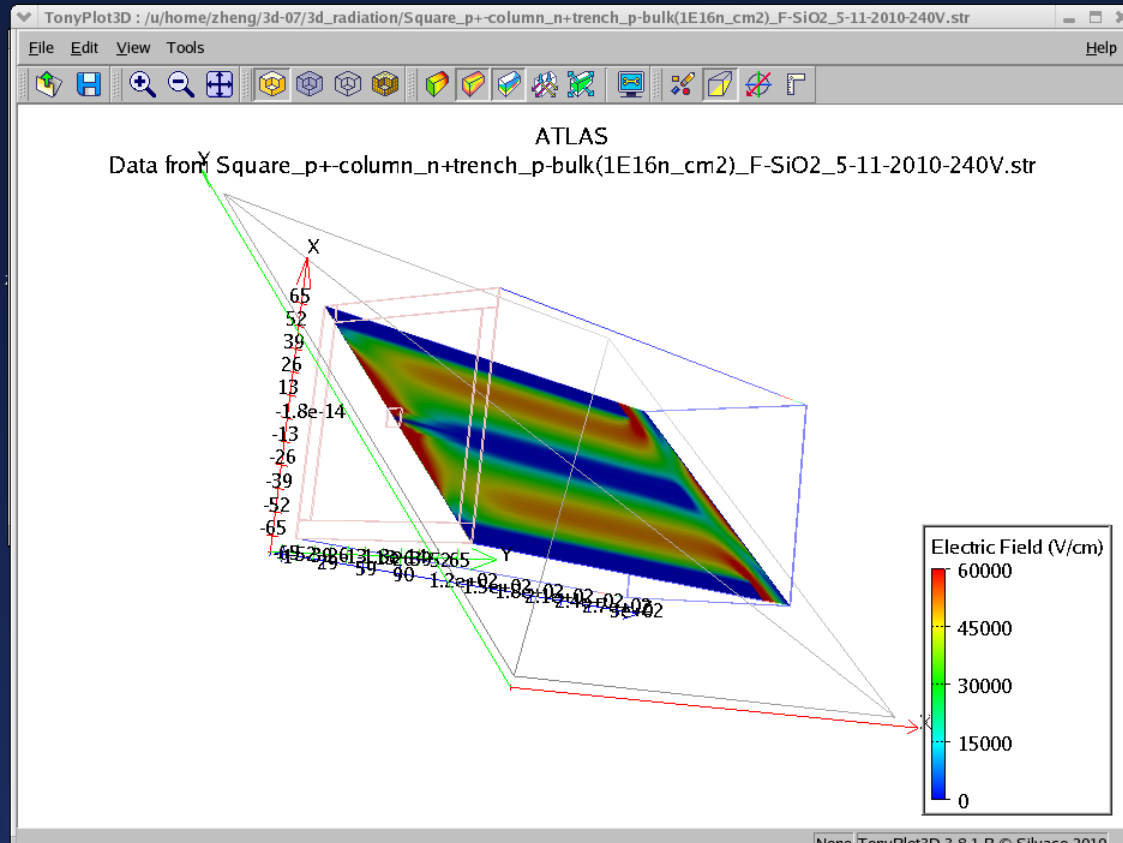
Plane from Square_p+column_n+trench_p-bulk(1E16n_cm2)_F-SiO2_5-11-2010-240V

X-axis values: 0, 3e+02

Y-axis values: 0, 1.8e+02

Electric Field (V/cm) Legend:
15000
7500
0





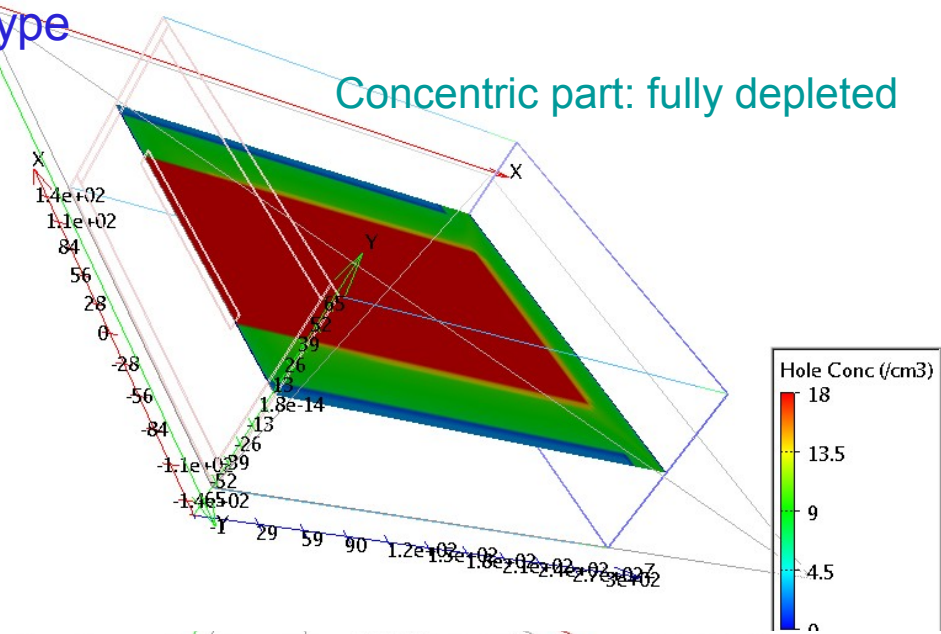
Data from Rec_p+10x160-ct_280um-t_p-bulk(1E16n)_50um-s_5-20-10-240V.str

Linear type

Concentric part: fully depleted

Materials:

- SiO₂
- Aluminum
- Silicon

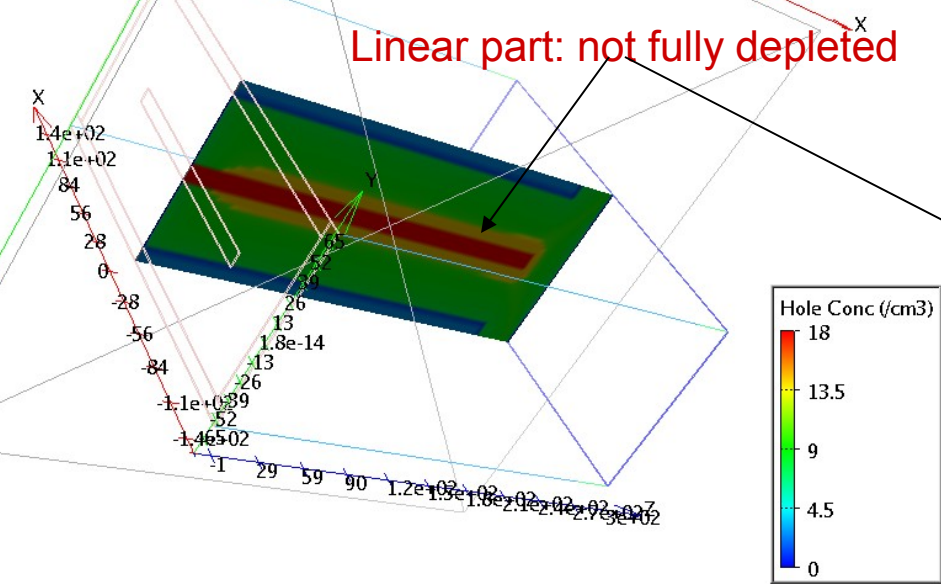


Data from Rec_p+10x160-ct_280um-t_p-bulk(1E16n)_50um-s_5-20-10-240V.str

Linear part: not fully depleted

Materials:

- SiO₂
- Aluminum
- Silicon



Elevation: 0 -1 1

Drag Type: Interactive

Cutplane Coordinates

P1.x	0	P1.y	0.0	P1.z	0.0
P2.x	0	P2.y	1	P2.z	0
P3.x	0	P3.y	0	P3.z	1

Update...

Axes Settings

Reverse X Reverse Y Swap X-Y

Cut Plane from Rec_p+10x160-ct_280um-t_p-bulk(1E16n)_50um-s_5-20-10-240V...

Materials:

- SiO₂
- Aluminum
- Silicon

Elevation: 0 -1 1

Drag Type: Interactive

Cutplane Coordinates

P1.x	0	P1.y	0.0	P1.z	0.0
P2.x	0	P2.y	1	P2.z	0
P3.x	0	P3.y	0	P3.z	1

Update...

Axes Settings

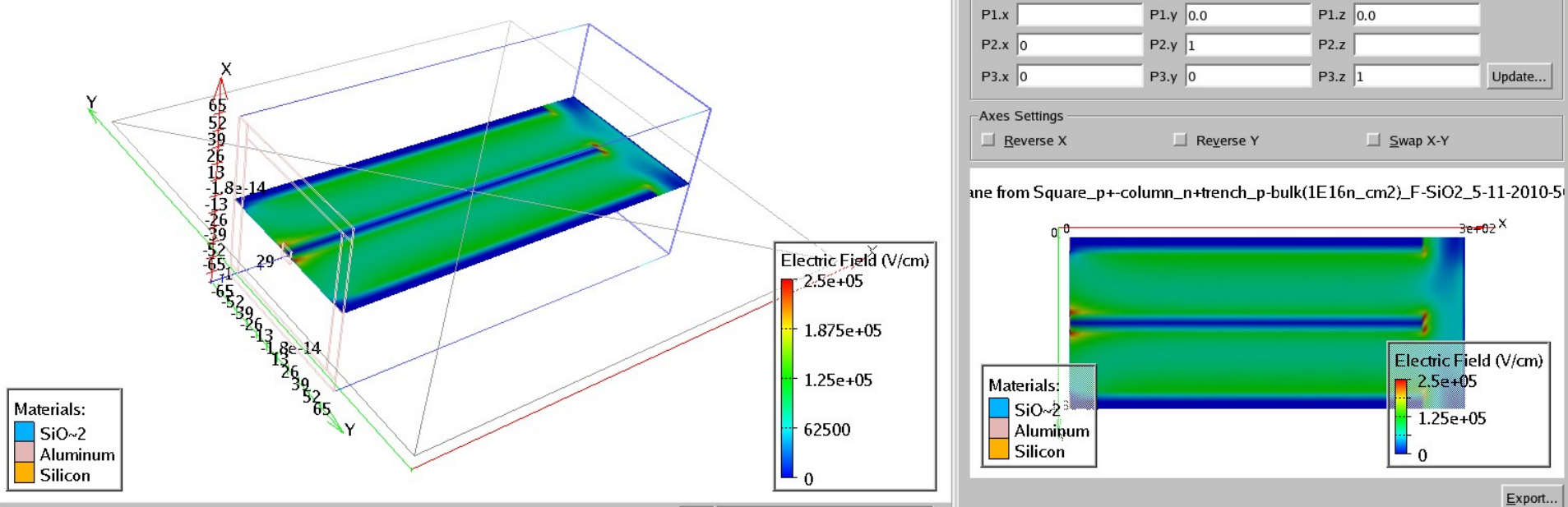
Reverse X Reverse Y Swap X-Y

Cut Plane from Rec_p+10x160-ct_280um-t_p-bulk(1E16n)_50um-s_5-20-10-240V...

Materials:

- SiO₂
- Aluminum
- Silicon

Export...

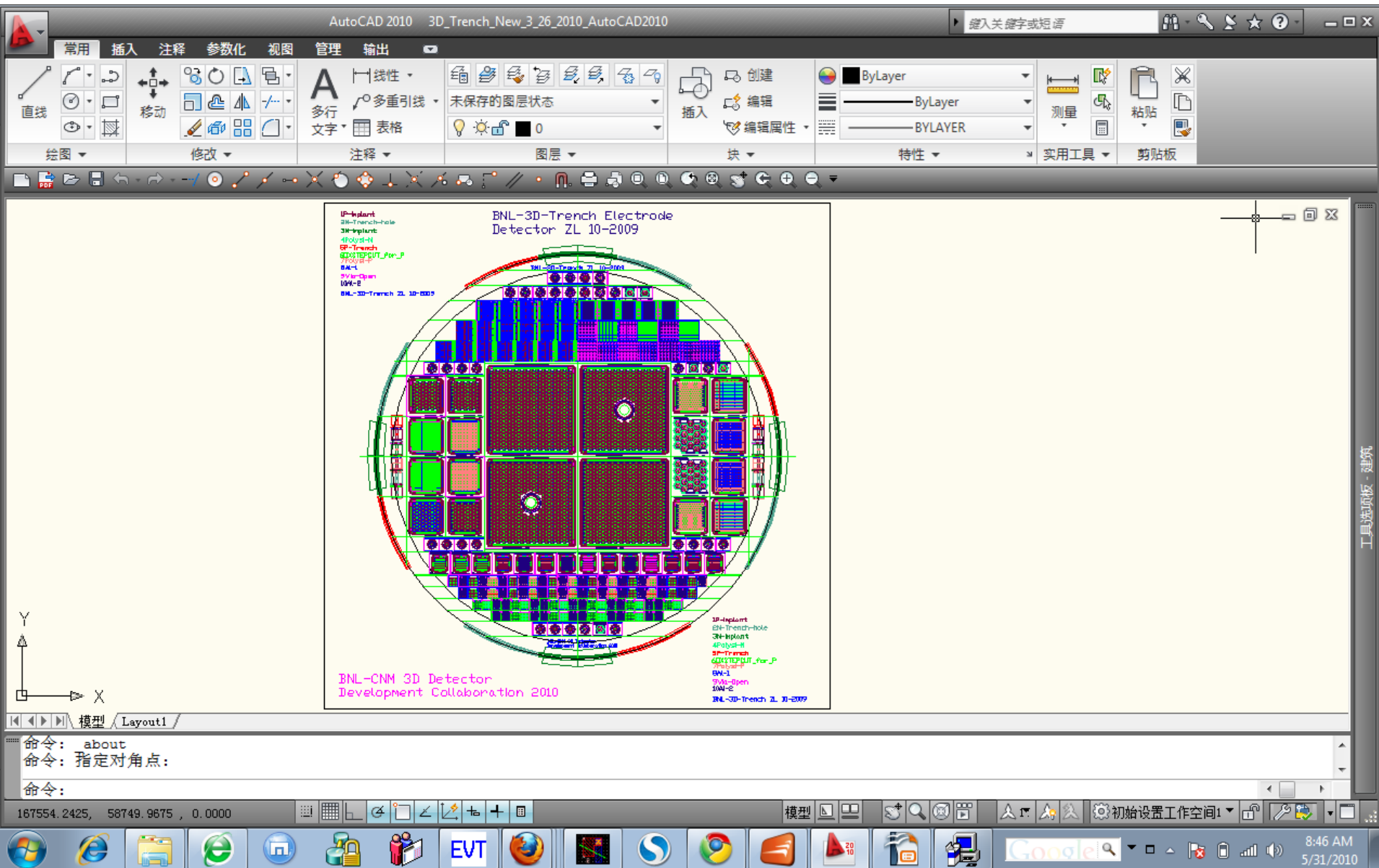


The highest E-field is under the junction trench, and near and under the column at about 250 kV/cm at a bias 260V over-full depletion. Over-bias mainly goes to the column region where the low field was originally ---- resulting in a near uniform E-field in the bulk.

The highest E-field is under the junction column >700 kV/cm (500V) for STD 3D and 3D-Trench with central-column junction.

Mask design almost finished

1st prototype will be processed at CNM



• Summary

- ❑ New Independent Coaxial Detector Array (ICDA) with novel, asymmetric trench electrodes has more homogeneous E-field
- ❑ The best configuration is the concentric type with the junction on the outer ring trench (ICDA-ORJ) --- electric field manipulation
- ❑ The electric field distribution in a ICDA-ORJ detector is even more uniform, and full depletion voltage is even lower than those in 2D planar detectors
- ❑ At full depletion the central column is well isolated and the volume under the trench/column are fully depleted as well, providing sensitivity in the volume
- ❑ Small area in collection electrode and intrinsic pixel isolations in ICDA-ORJ detectors provide other advantages in detector applications